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Electron transport in molecules, nanotubes and graphene

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Electron Transport in Molecules, Nanotubes and Graphene

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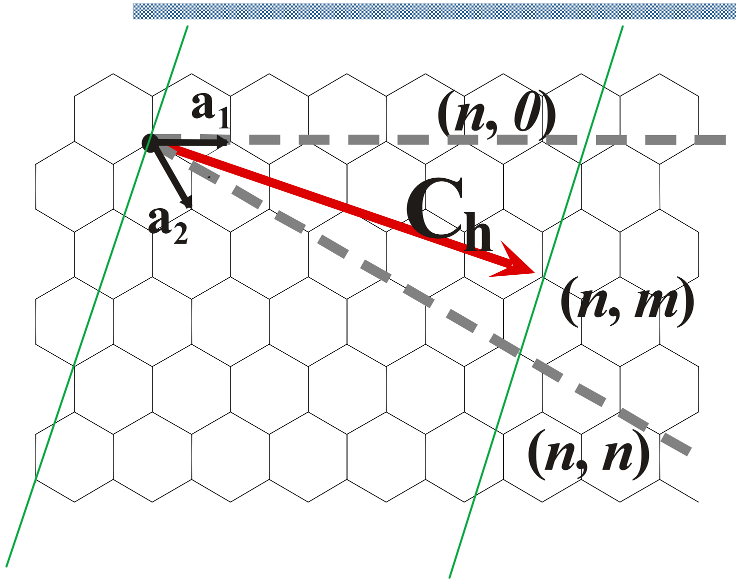
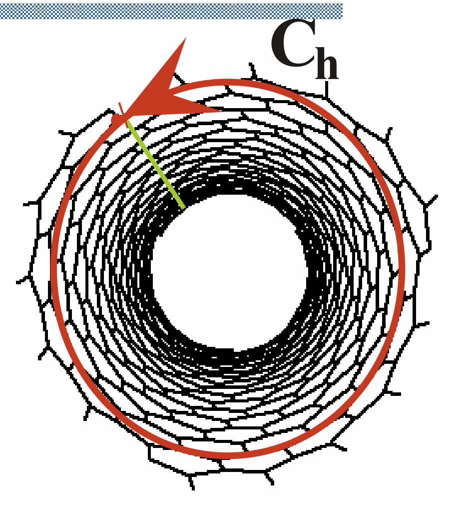
IN THE CITY OF NEW YORK

Columbia University and the National Science Foundation
Center for Electron Transport in Molecular Nanostructures

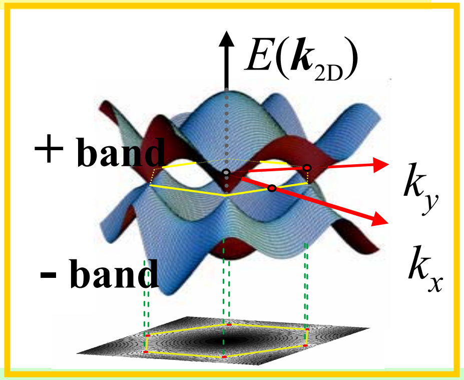
Rolling Up Graphene: Periodic Boundary Condition

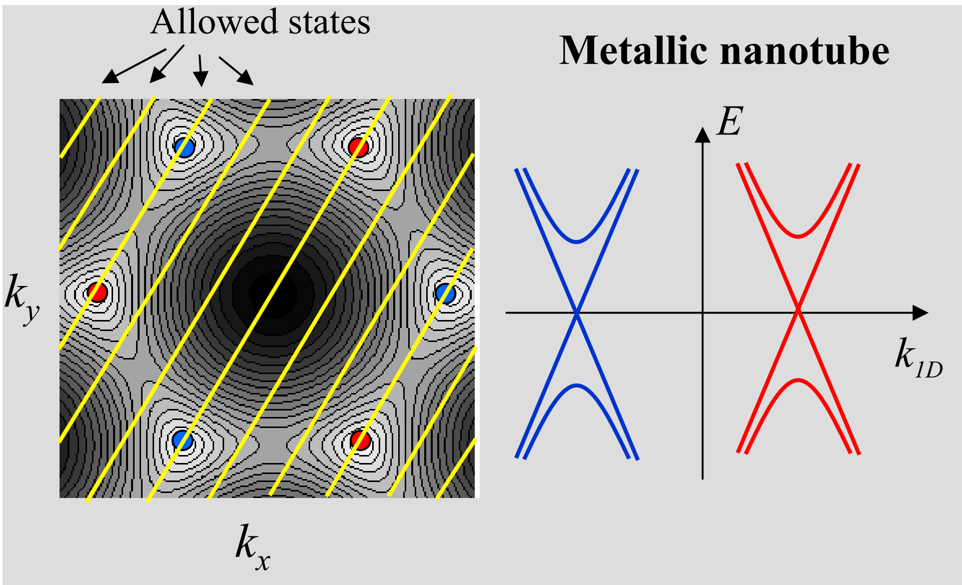


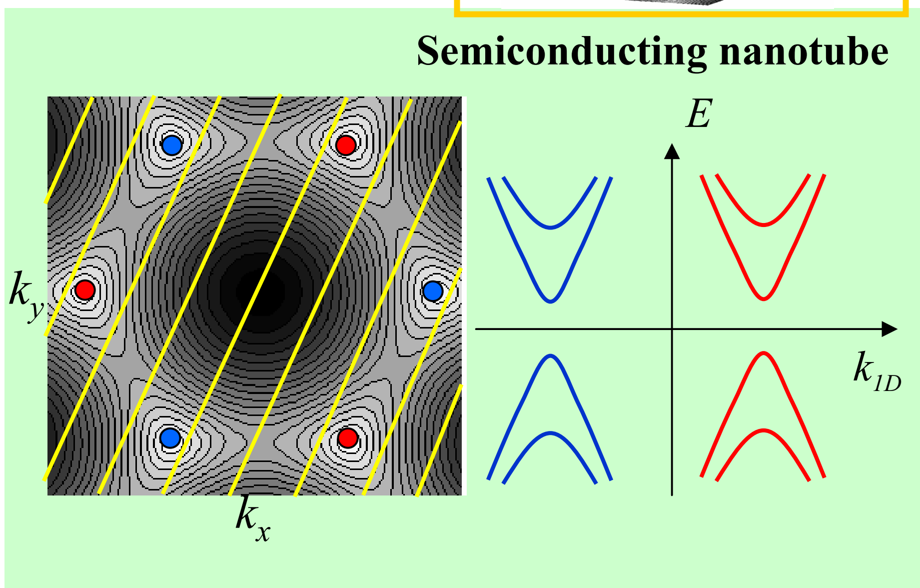


Periodic Boundary Condition

$$C_h \cdot \vec{k}_{\perp} = 2\pi q$$

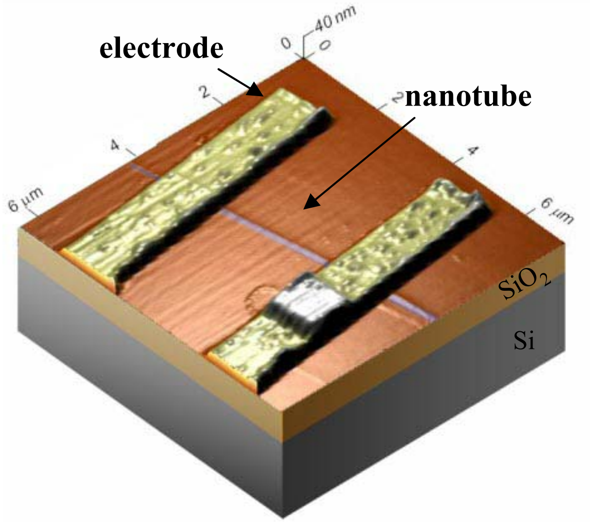


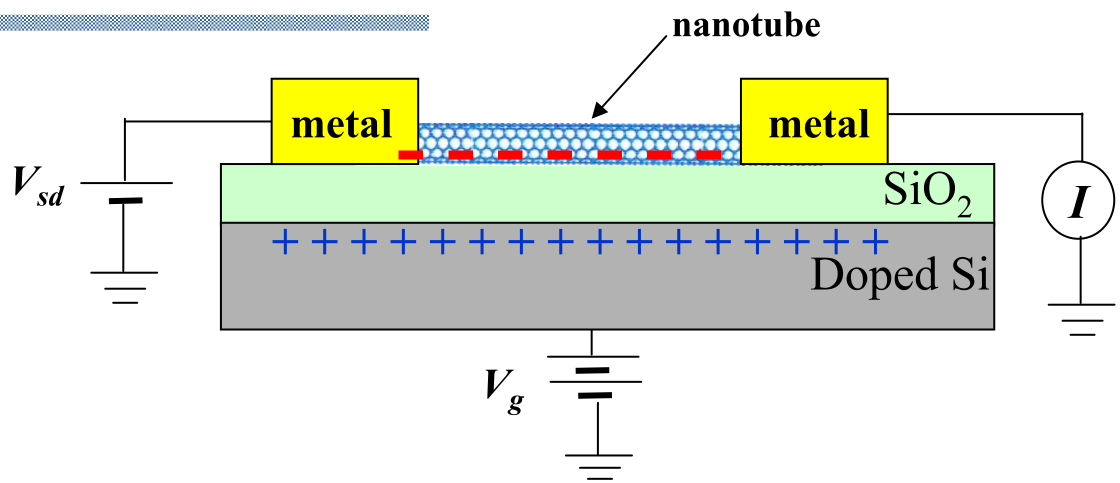




Tuning Carrier Density by Electric Field Effect

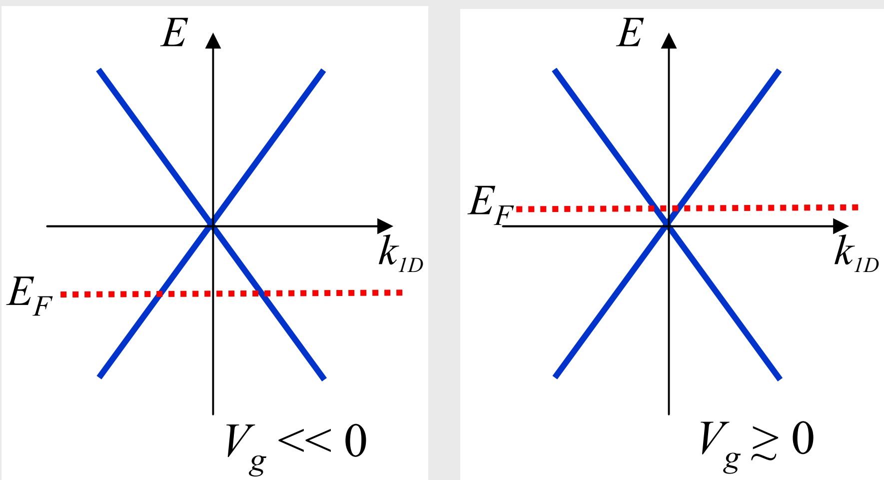
Atomic force microscope image of nanotube device



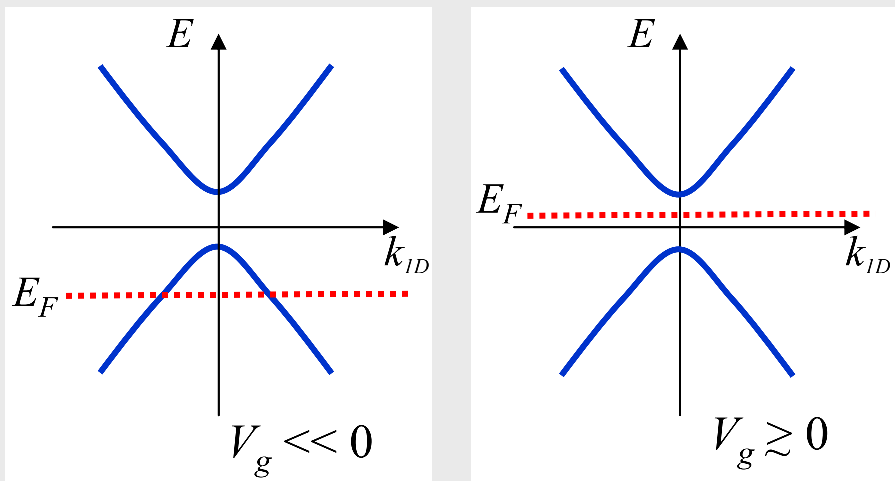


Induced charge: $C_g\, V_g = e\, n = e\,(\mathrm{D.O.S})\, \Delta E_F$

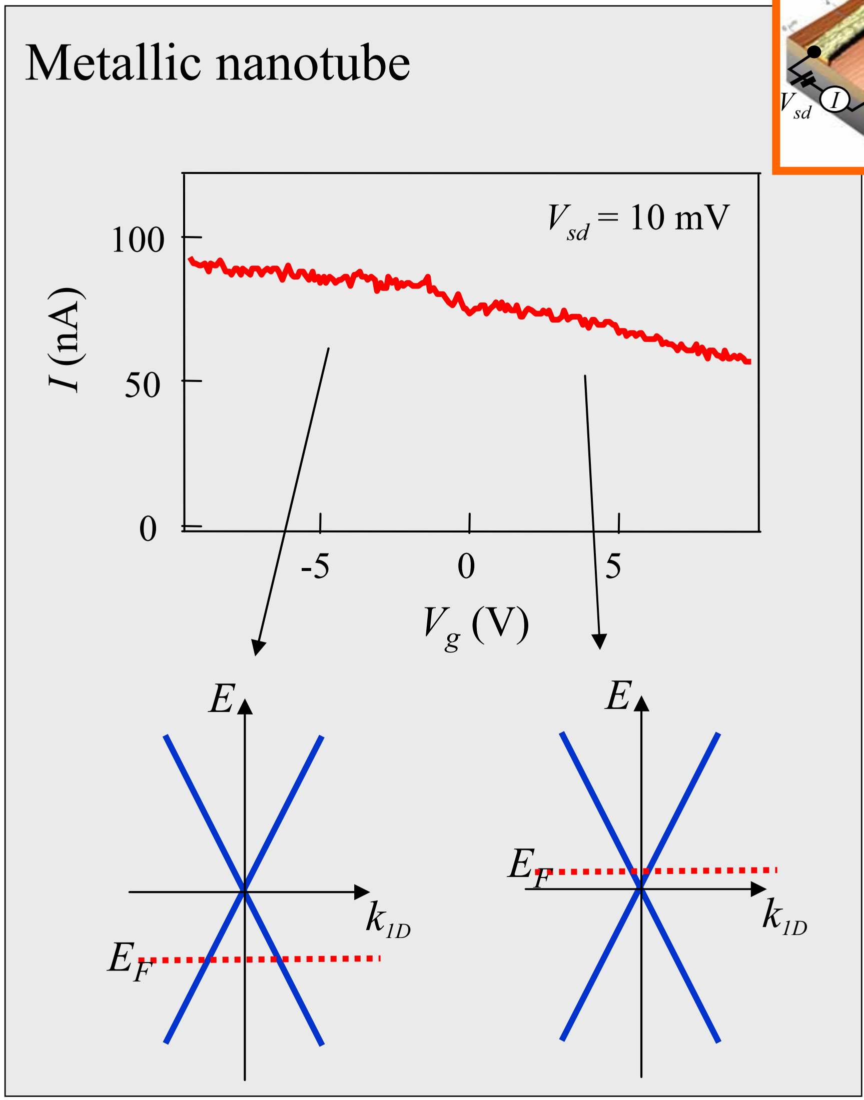
Metallic nanotube

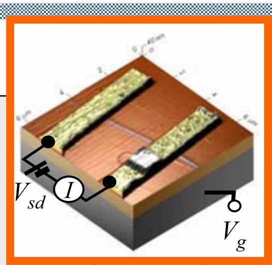


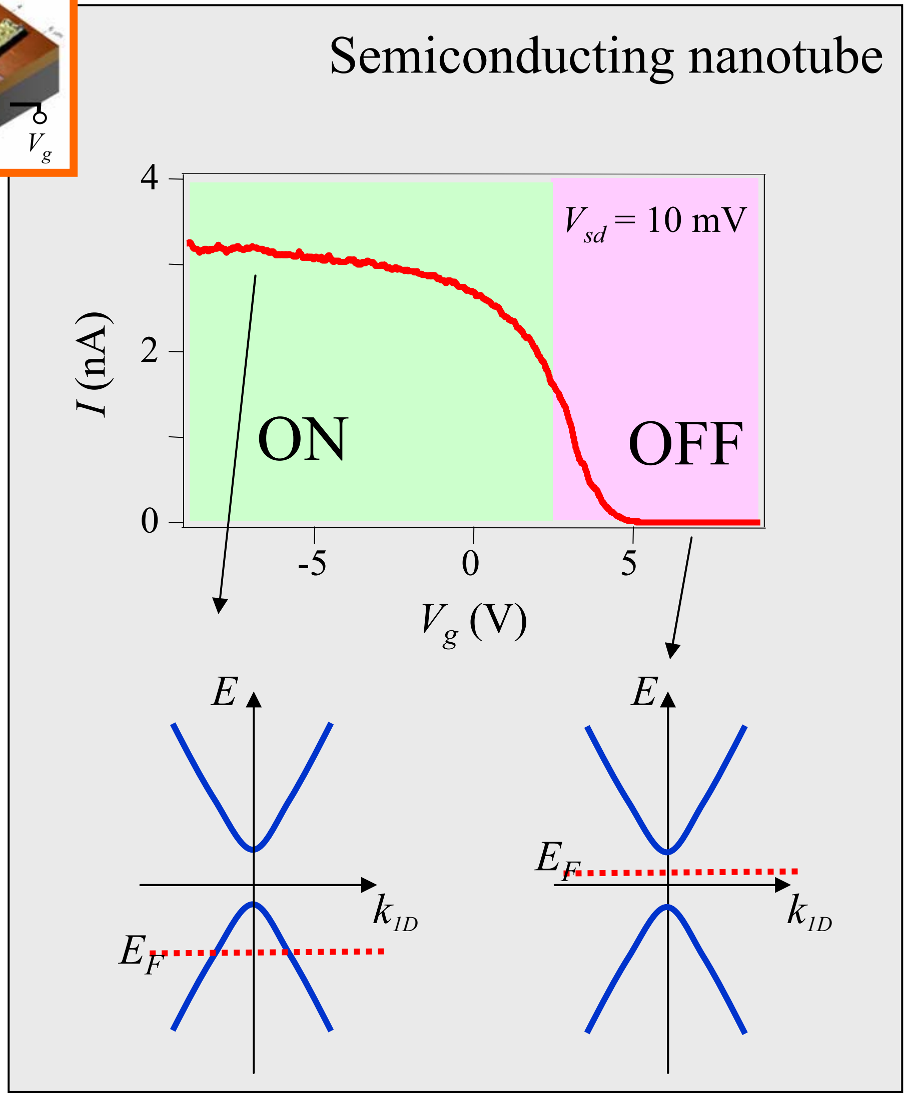
Semiconducting nanotube



Electrical Transport in Nanotube Devices







Controlled Growth of Ultralong Nanotubes

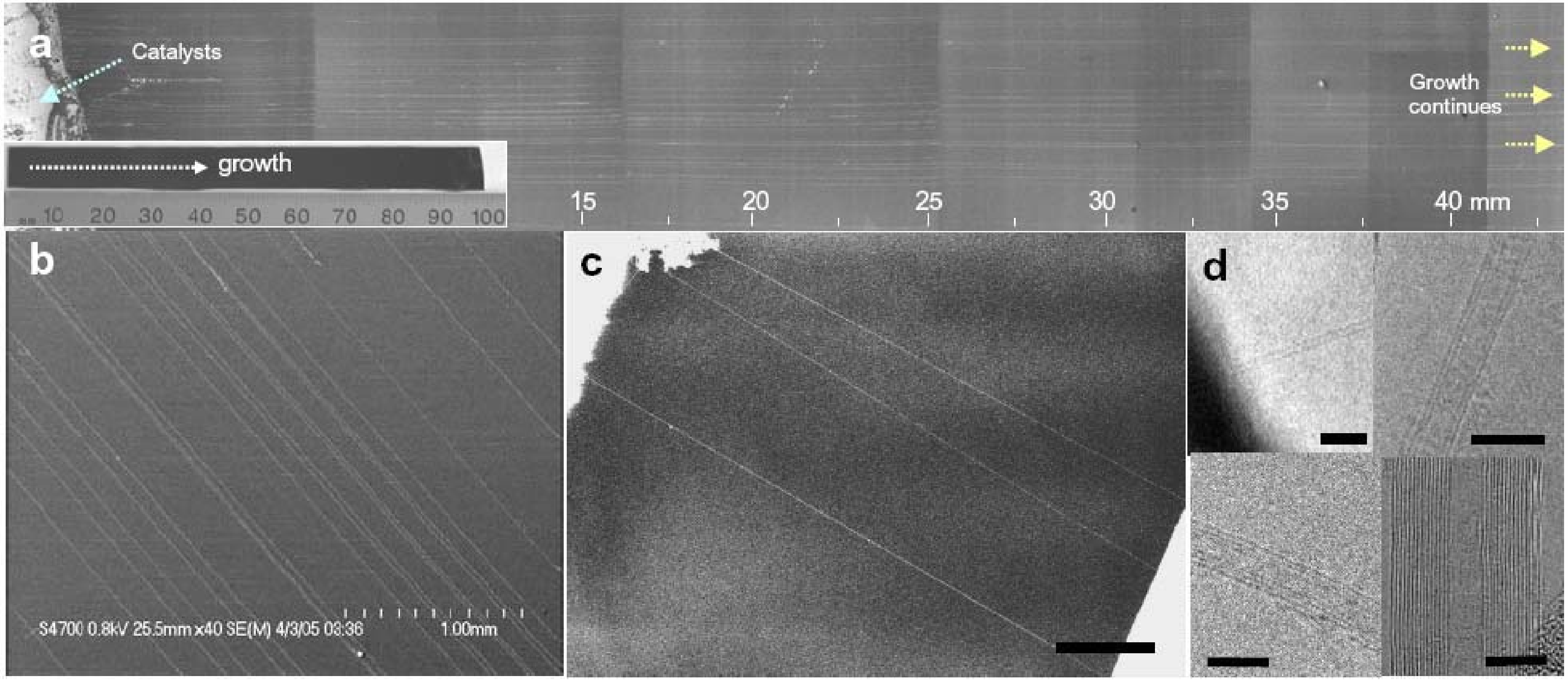
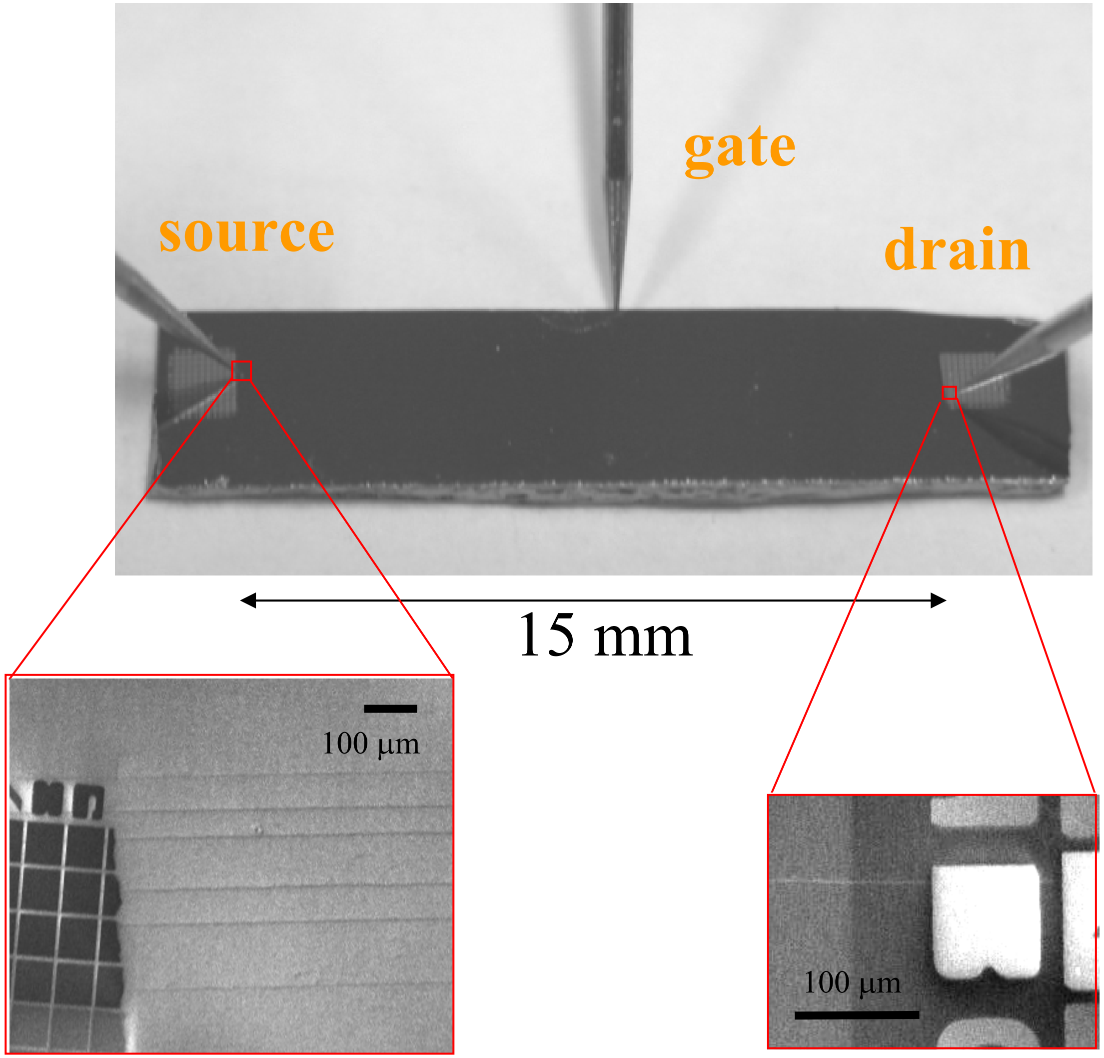


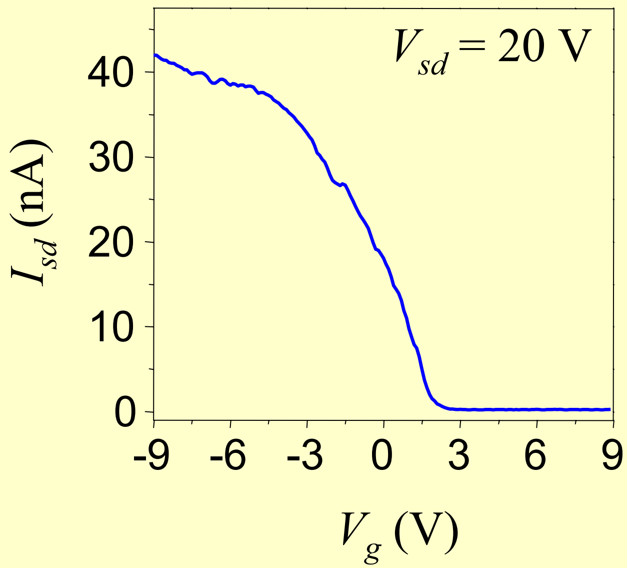
Figure 3. SEM and TEM images of ultralong MWNTs. (a) Schemetic representation for the diameter-dependent stabilization of reaction gas flows. By inserting the smaller tube inside the outer chamber, microscopic turbulent flows can be stabilized into laminar flows with lower Reynolds numbers. (b) SEM image of MWNTs, which are several centimeters long. Scale bar, 2mm. (c) A SEM image of MWNTs grown across a 100 µm slit. Scale bar, 20µm. D, HRTEM images showing single, double, triple, and multi-walled CNTs. Scale bars, 5 nm.

B. H. Hong, J. Y. Lee, T. Beetz, Y. Zhu, P. Kim and S. Kim (2005)

Extremely Long SWNT Field Effect Transistor



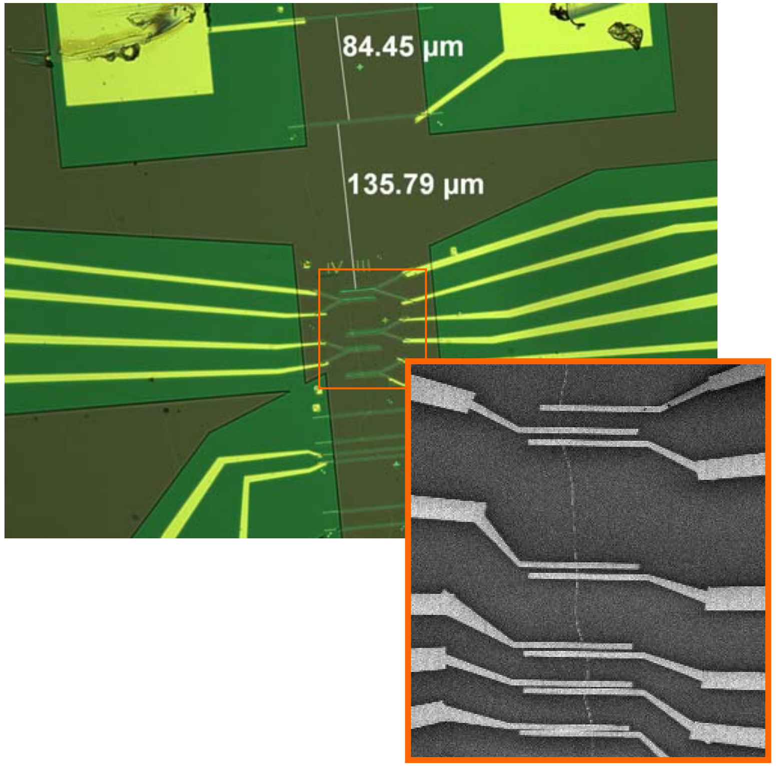
FET characteristics

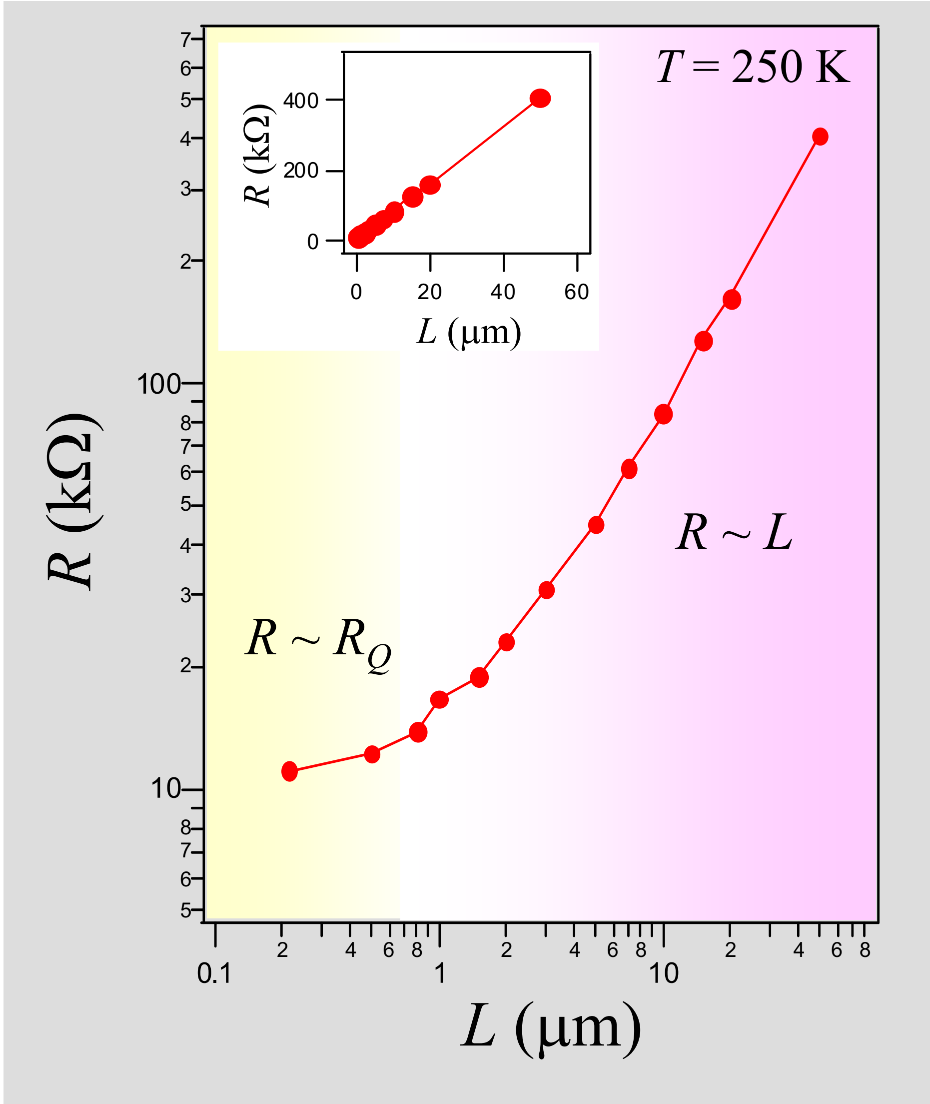


$\rho \sim 10^{-7}\ \Omega\ \mathrm{m}$

Electron Transport in Long Single Walled Nanotubes

Multi-terminal Device with Pd contact



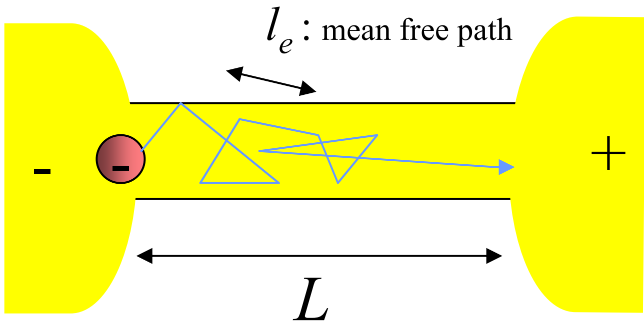


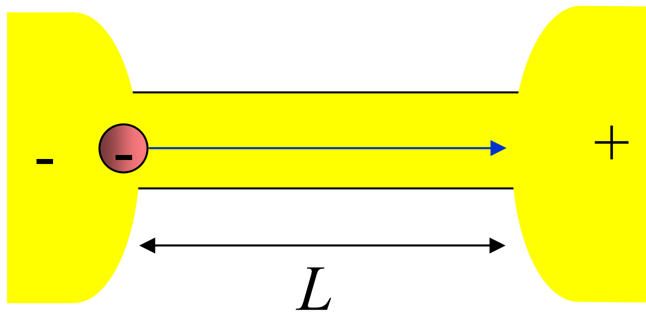
* Scaling behavior of resistance: $R(L)$

M. Purewall, A. Ravi, and P. Kim (2006)

Ballistic Transport and Mean Free Path

Electron Transport in 1D Channel





Diffusive transport: $l_e << L$

$$R(L) = \rho L$$

Ballistic transport: $L < l_e$

$$R(L) = h / N e^2 = R_Q$$

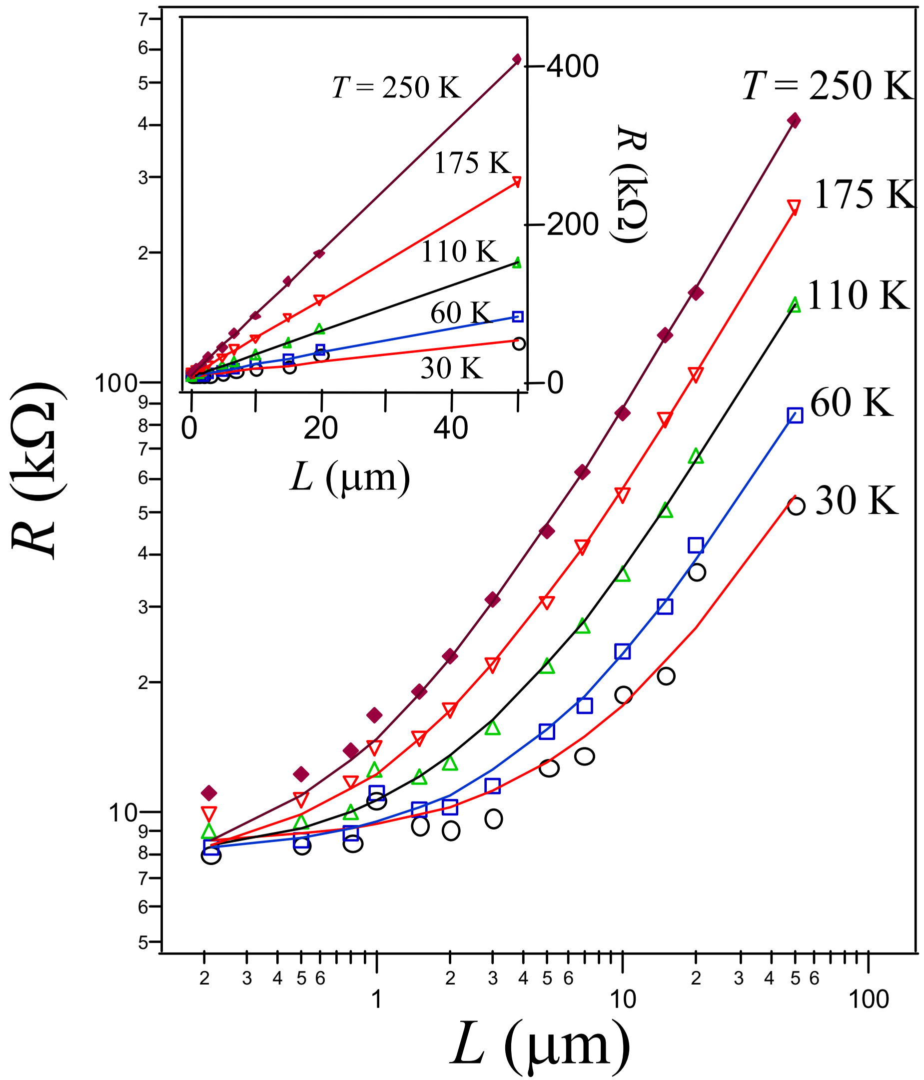
\# of channel

Resistance of N- 1D Channel:

$$R(L) = \frac{h}{Ne^2} + \frac{h}{Ne^2}\frac{L}{l_e}$$

For a nanotube, $N = 4$ (2 from spin and 2 from ***K*** and ***K'***)

Electron Mean Free Path of Nanotube

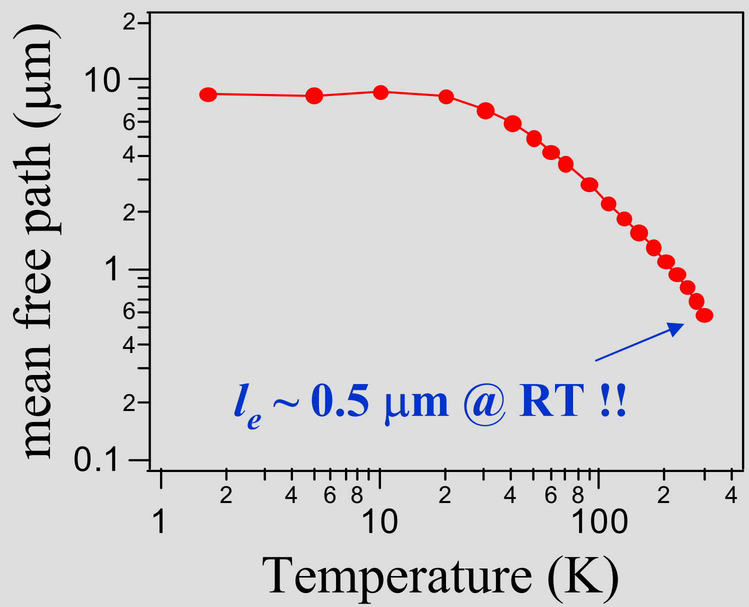


Lines are fit to

$$R(L) = R_c + \frac{h}{4e^2} + \frac{h}{4e^2}\frac{L}{l_e}$$

$$\frac{h}{4e^2} = 6.45\ \text{k}\Omega$$

Non-ideal contact resistance $R_c < 2$ kΩ



Extremely Long Mean Free Path: Hidden Symmetry ?

Carbon nanotube:

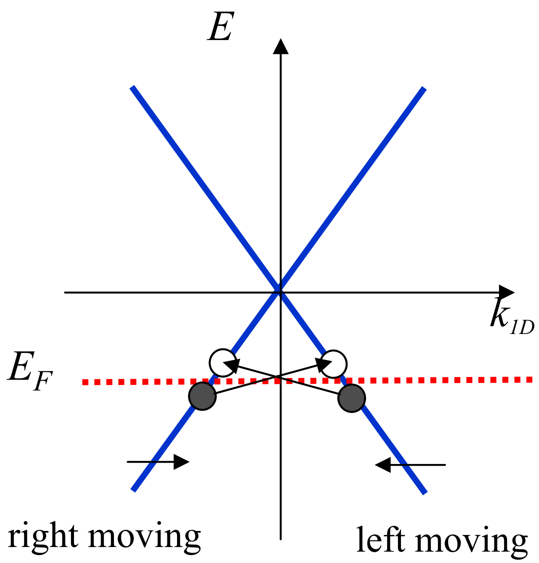
$l_e \sim$ **10 μm @ 1.6 K**

$l_e \sim$ **0.5 μm @ 300 K**

Ga[Al]As HEMT:

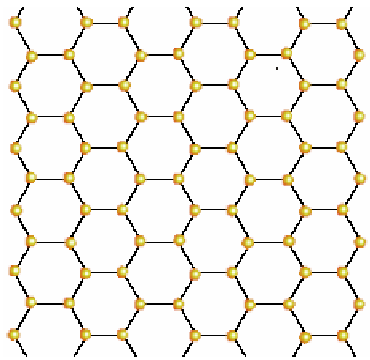
$l_e \sim$ **100 μm @ 1.6 K**

$l_e \sim$ **0.06 μm @ 300 K**



•Small momentum transfer backward scattering must be inefficient.

Selection rules by hidden symmetry in graphene?



T. Ando, JPSJ (1998);McEuen at al, PRL (1999)

Electric Field Effect in Mesoscopic Graphite

APPLIED PHYSICS LETTERS **86**, 073104 (2005)

Fabrication and electric-field-dependent transport measurements of mesoscopic graphite devices

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(Received 31 August 2004; accepted 11 December 2004; published online 7 February 2005)

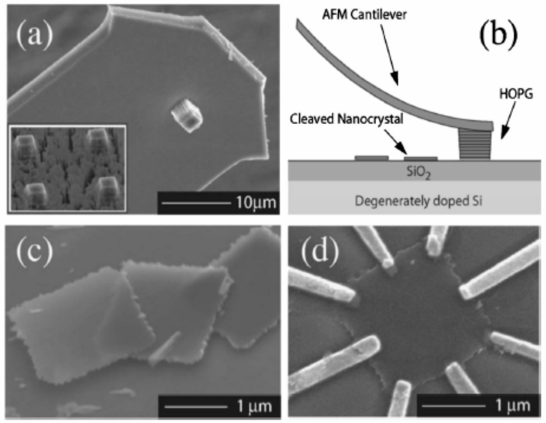
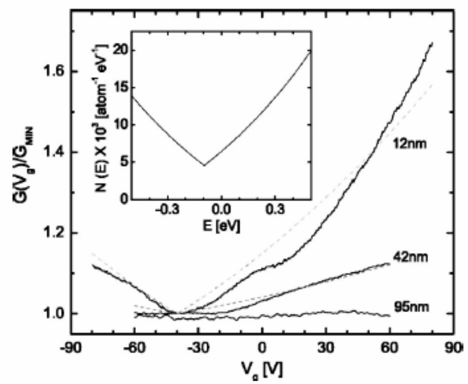


FIG. 1. (a) Scanning electron microscope image of an HOPG crystallite mounted on a microcantilever. Inset: bulk HOPG surface patterned by masked anisotropic oxygen plasma etching; (b) schematic drawing of the microcleaving process; (c) thin graphite samples cleaved onto the SiO_2/Si substrate; (d) a typical mesoscopic device fabricated from a cleaved graphite sample.



PRL **94**, 176803 (2005) PHYSICAL REVIEW LETTERS week endi
6 MAY 2(

Electric Field Modulation of Galvanomagnetic Properties of Mesoscopic Graphite

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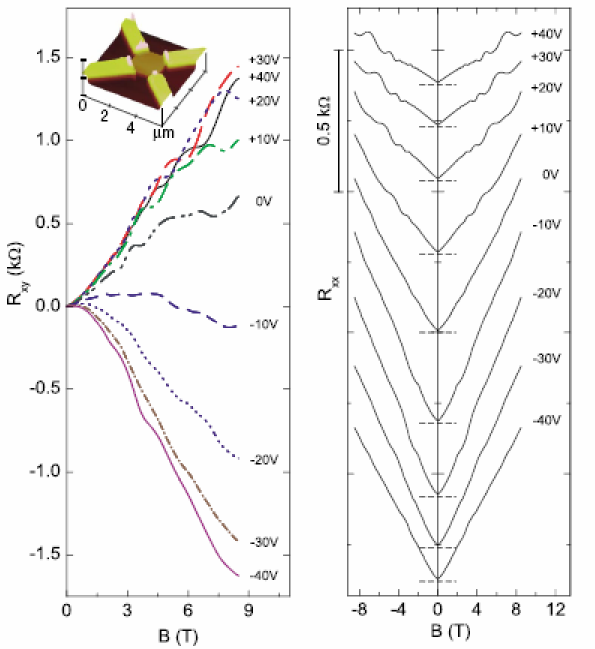
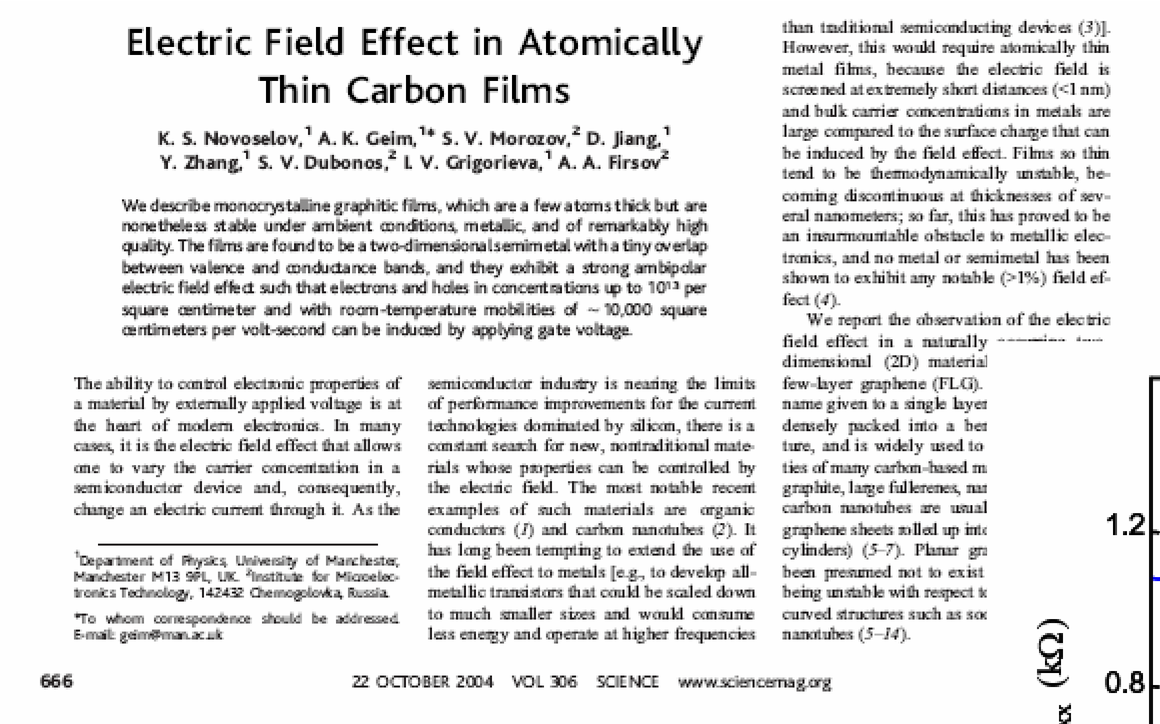
Department of Physics and the Columbia Nanoscale Science and Engineering Center, Columbia University, New York, New York 10027, USA
(Received 31 August 2004; published 3 May 2005)



Simple Yet Efficient Mechanical Extraction



Electric Field Effect in Atomically Thin Carbon Films

K. S. Novoselov,[1] A. K. Geim,[1*] S. V. Morozov,[2] D. Jiang,[1] Y. Zhang,[1] S. V. Dubonos,[2] I. V. Grigorieva,[1] A. A. Firsov[2]

We describe monocrystalline graphitic films, which are a few atoms thick but are nonetheless stable under ambient conditions, metallic, and of remarkably high quality. The films are found to be a two-dimensional semimetal with a tiny overlap between valence and conductance bands, and they exhibit a strong ambipolar electric field effect such that electrons and holes in concentrations up to 10^{13} per square centimeter and with room-temperature mobilities of ~10,000 square centimeters per volt-second can be induced by applying gate voltage.

The ability to control electronic properties of a material by externally applied voltage is at the heart of modern electronics. In many cases, it is the electric field effect that allows one to vary the carrier concentration in a semiconductor device and, consequently, change an electric current through it. As the semiconductor industry is nearing the limits of performance improvements for the current technologies dominated by silicon, there is a constant search for new, nontraditional materials whose properties can be controlled by the electric field. The most notable recent examples of such materials are organic conductors (*1*) and carbon nanotubes (*2*). It has long been tempting to extend the use of the field effect to metals [e.g., to develop all-metallic transistors that could be scaled down to much smaller sizes and would consume less energy and operate at higher frequencies than traditional semiconducting devices (*3*)]. However, this would require atomically thin metal films, because the electric field is screened at extremely short distances (<1 nm) and bulk carrier concentrations in metals are large compared to the surface charge that can be induced by the field effect. Films so thin tend to be thermodynamically unstable, becoming discontinuous at thicknesses of several nanometers; so far, this has proved to be an insurmountable obstacle to metallic electronics, and no metal or semimetal has been shown to exhibit any notable (>1%) field effect (*4*).

We report the observation of the electric
field effect in a naturally
dimensional (2D) material
few-layer graphene (FLG).
name given to a single layer
densely packed into a ben
ture, and is widely used to
ties of many carbon-based m
graphite, large fullerenes, nan
carbon nanotubes are usual
graphene sheets rolled up into
cylinders) (*5–7*). Planar gra
been presumed not to exist
being unstable with respect t
curved structures such as soo
nanotubes (*5–14*).

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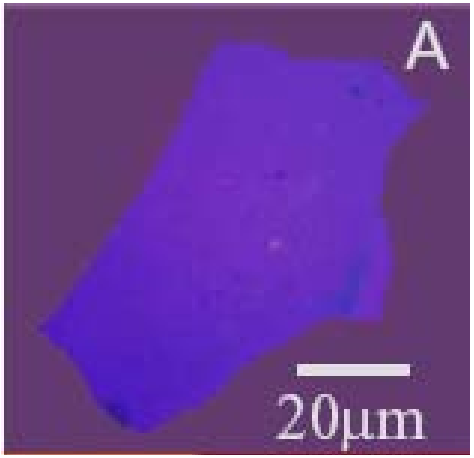
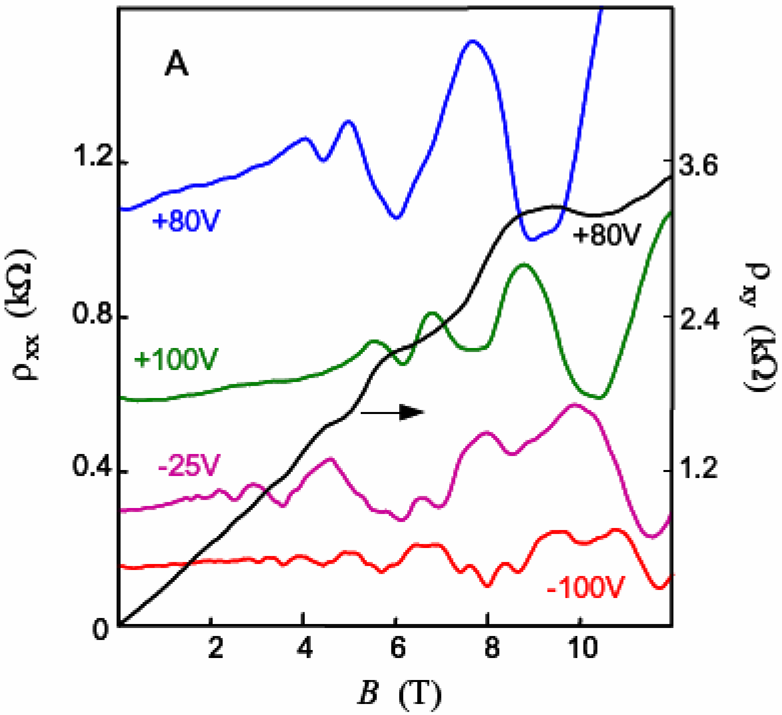
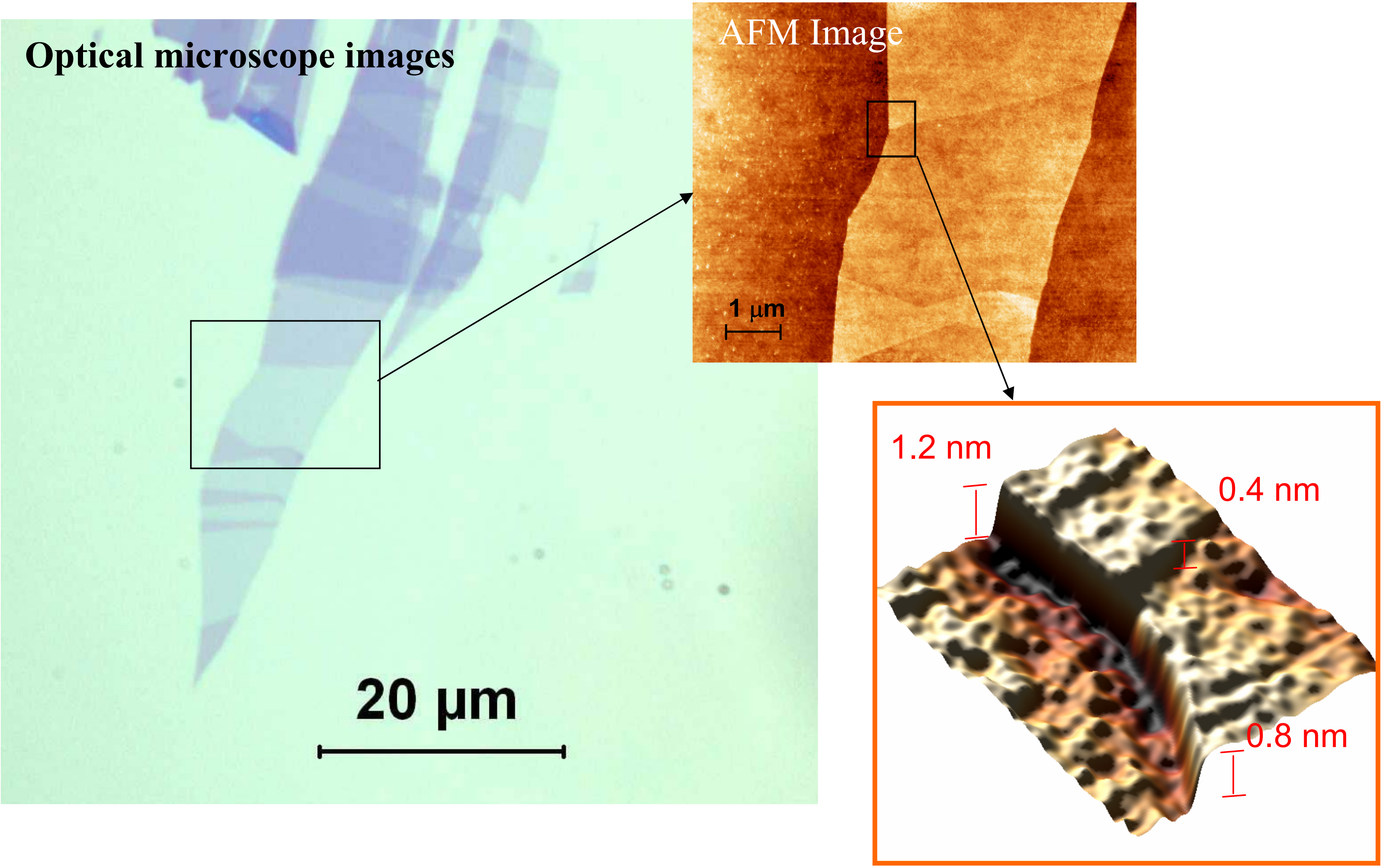


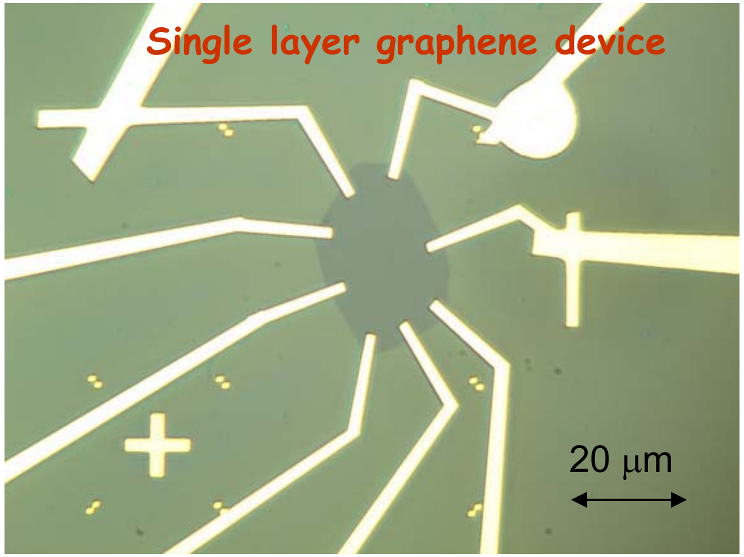


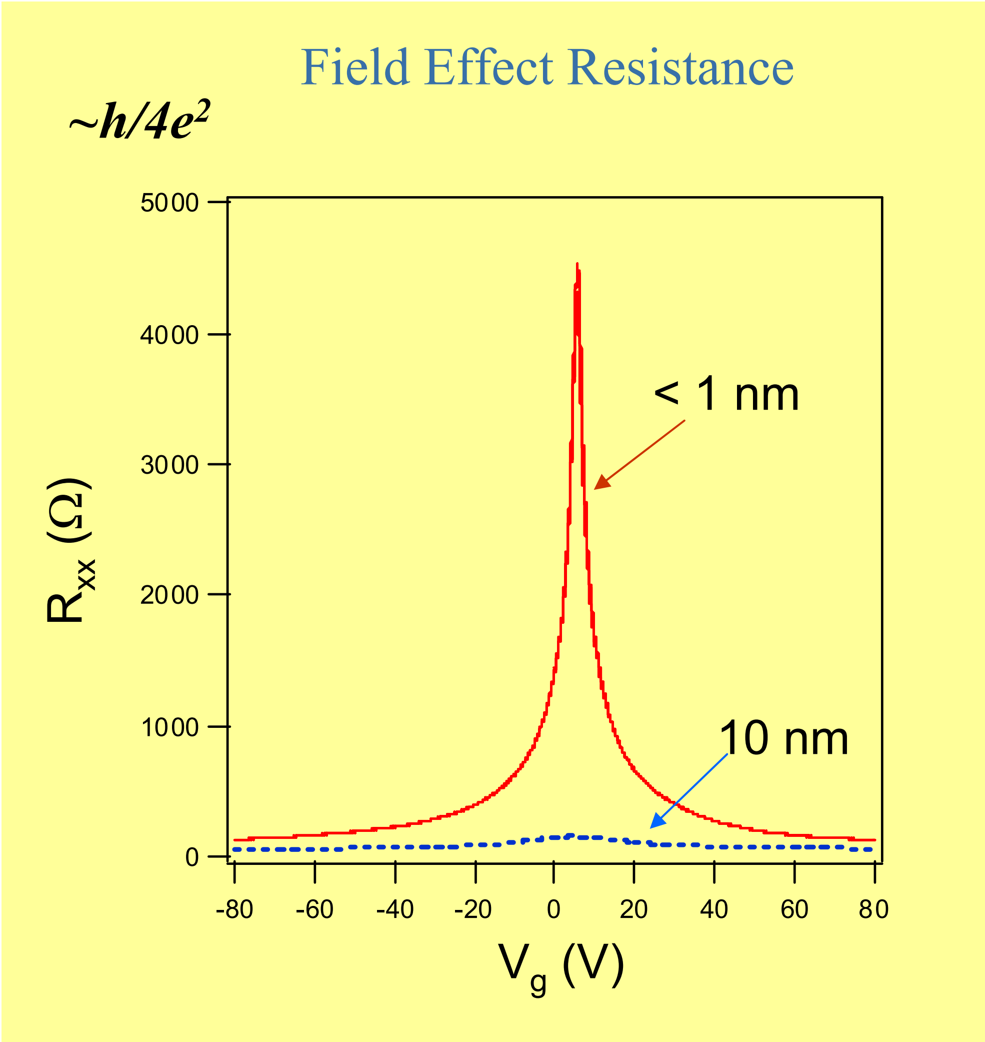
Using Scotch Tape is Essential!!

A Few Layer Graphene on SiO_2/Si Substrate



Transport Single Layer Graphene

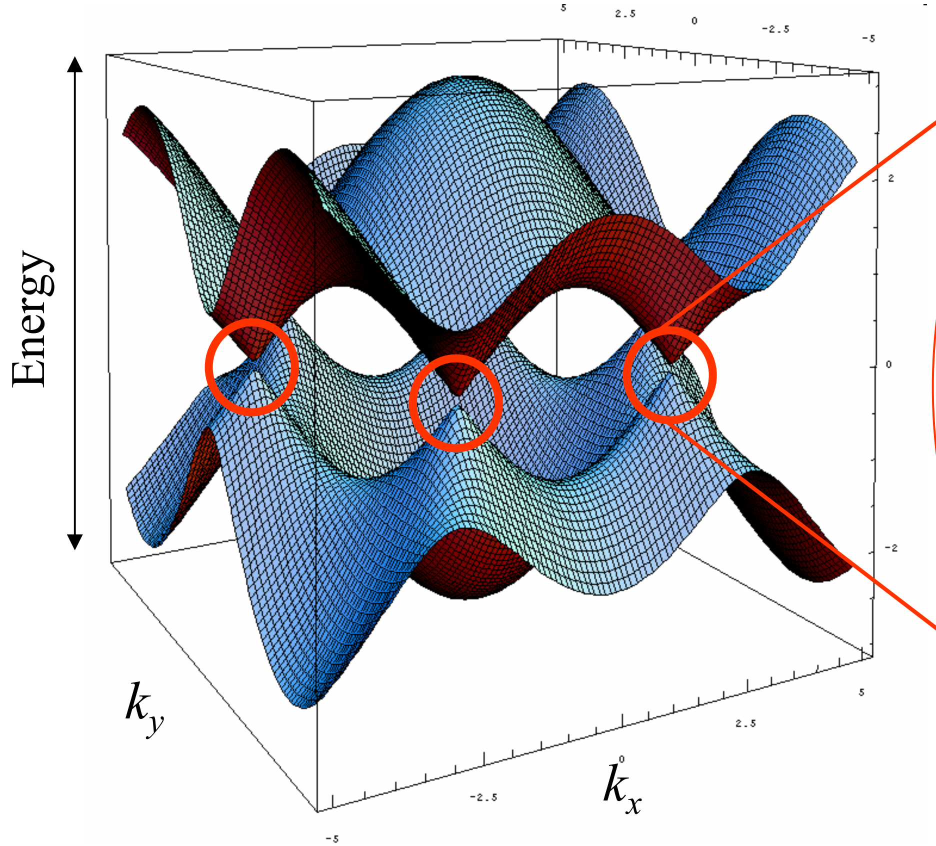


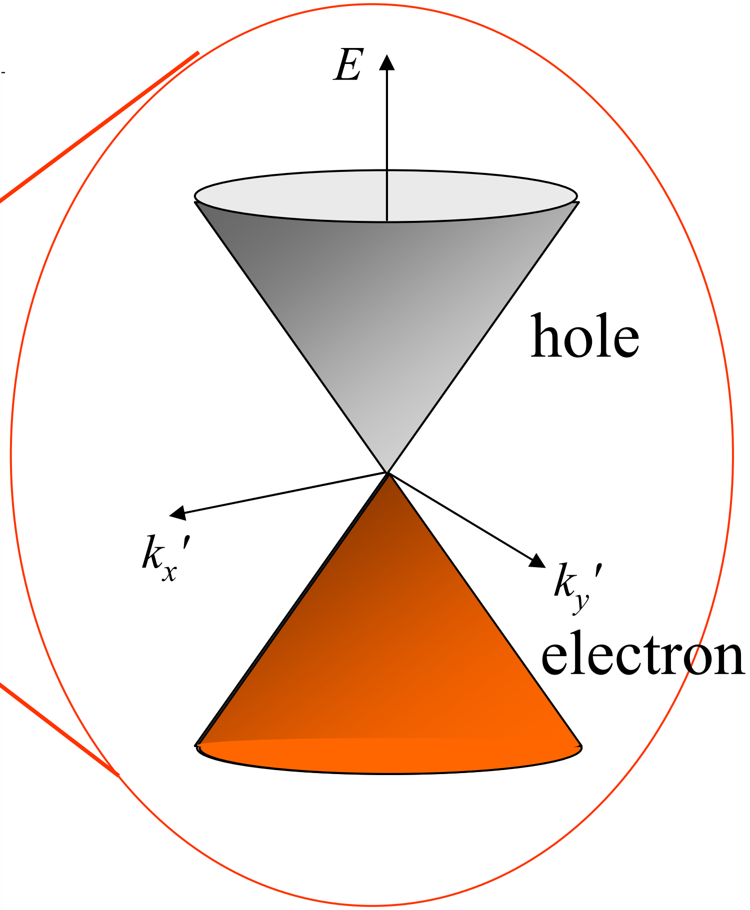


Zhang, Tan, Stormer & Kim (2005), see also Novoselov et al (2005).

Graphene : Dirac Particles in 2D Box

Band structure of graphene





$$E \approx \hbar v_F \left| \vec{k}'_{\perp} \right|$$

Massless Dirac Particles with effective speed of light v_F.

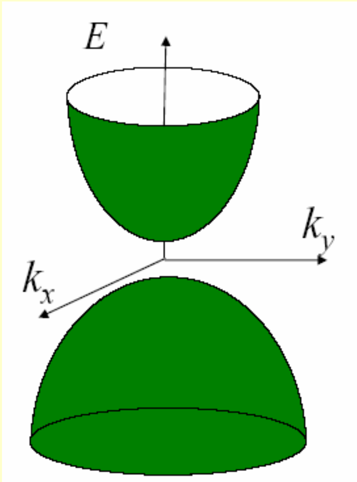
Graphene v.s. Conventional 2D Electron System

Band structures

Conventional 2D Electron System

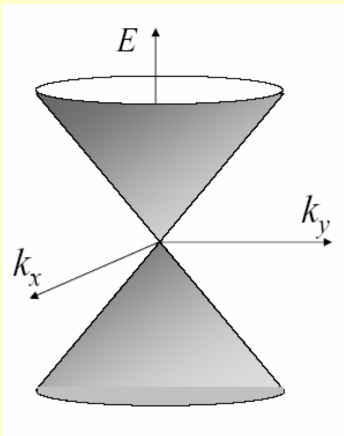
$$E = \frac{\hbar^2 k^2}{2m_e^*}$$

$$E = -\frac{\hbar^2 k^2}{2|m_h^*|}$$



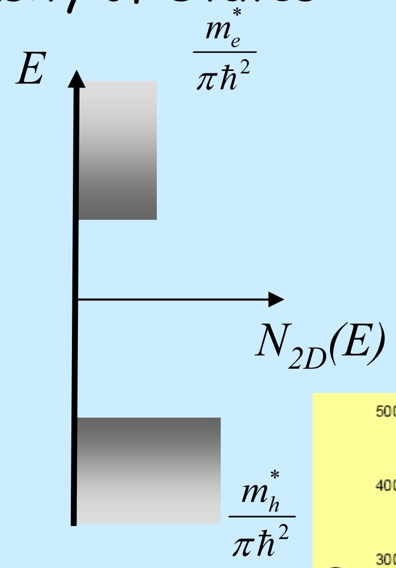
Graphene

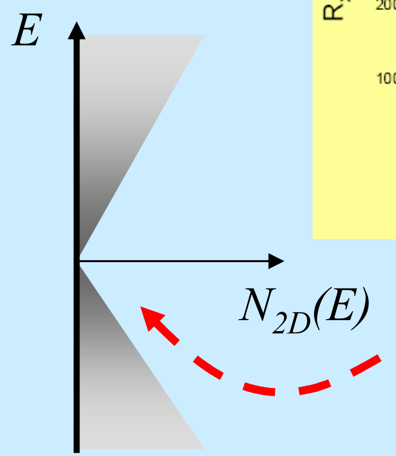
$$E = \hbar v_F |\vec{k}'_\perp|$$

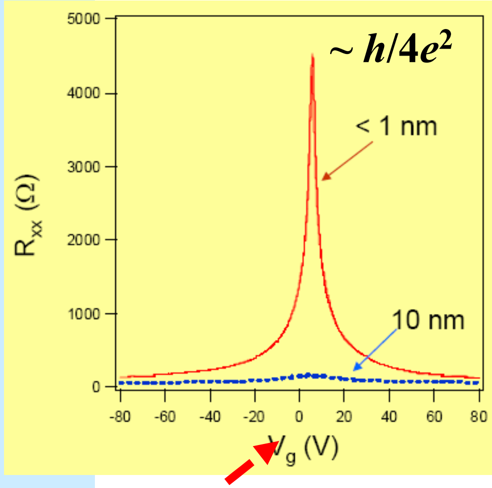


- Zero band mass
- Strict electron hole symmetry
- Electron hole degeneracy

Density of States



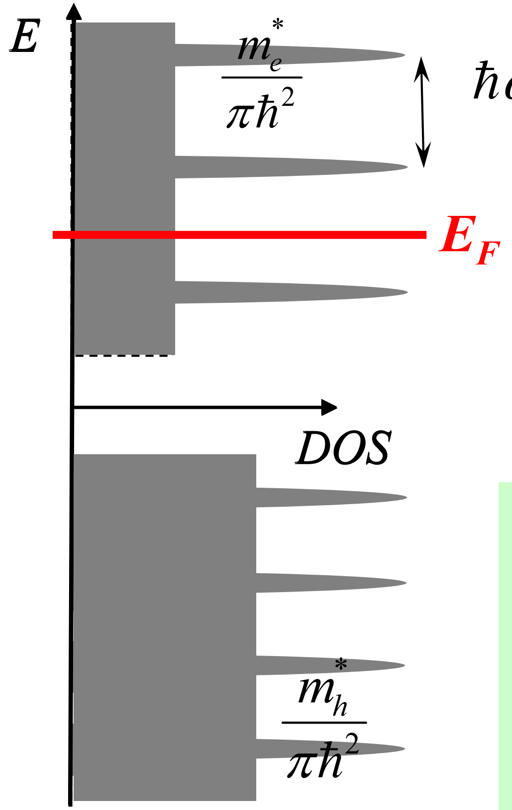




2D Gas in Quantum Limit : Conventional Case

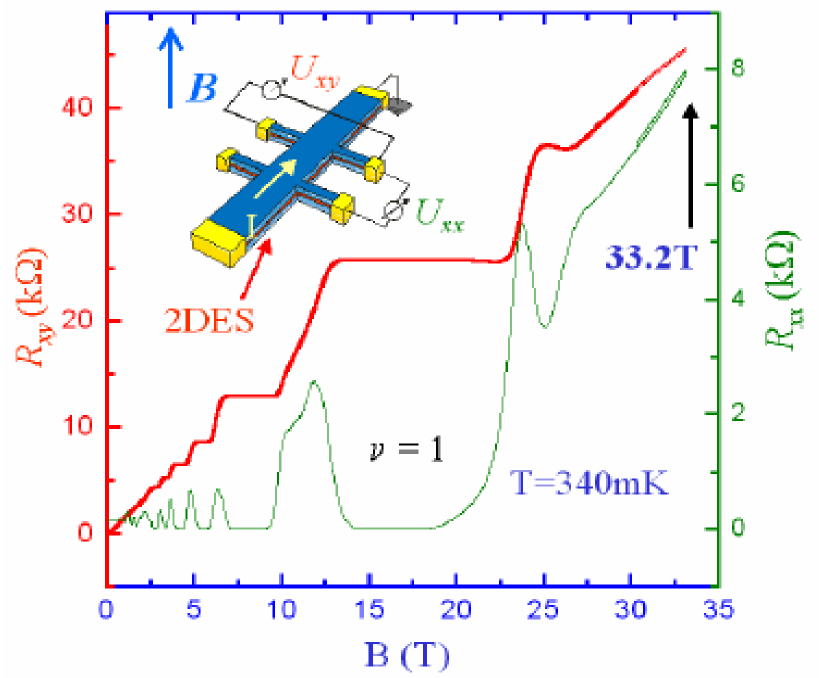
Density of States

Landau Levels in Magnetic Field



$$\hbar\omega_c = \hbar eB / m^*$$

Quantum Hall Effect in GaAs 2DEG



Integer Quantization:

$$R_{xy}^{-1} = \pm \nu \cdot g_s \cdot \frac{e^2}{h}$$

$$\nu = 1, 2, 3 \ldots$$

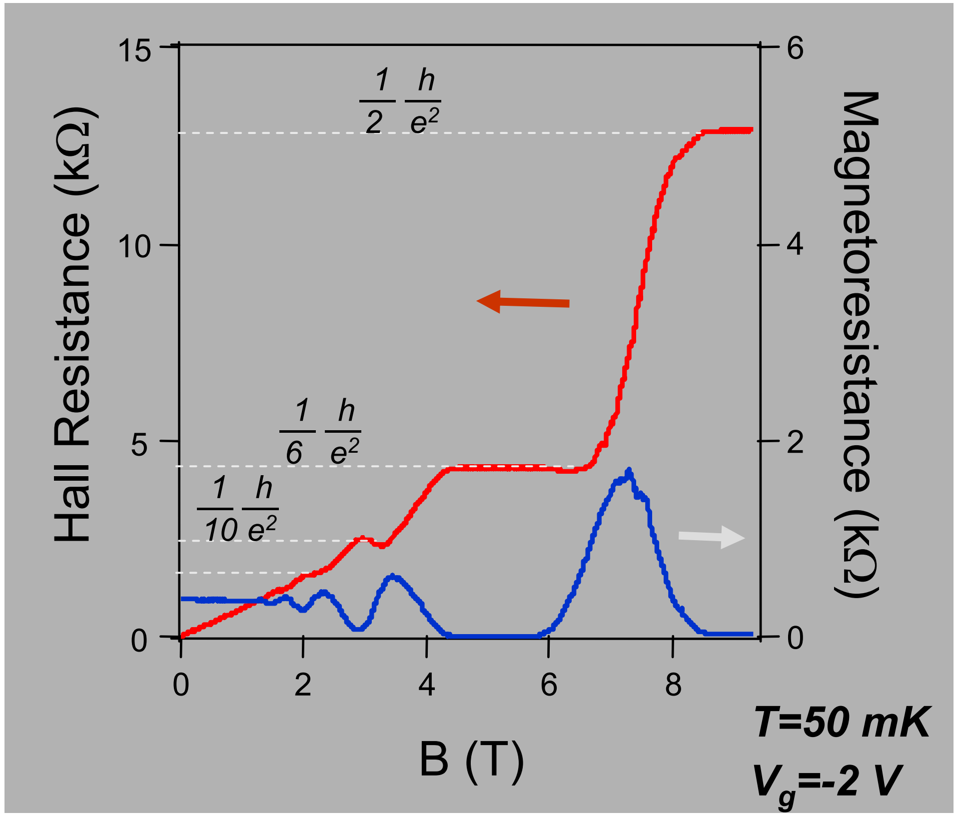
$$g_s = 2 \text{ (spin)}$$

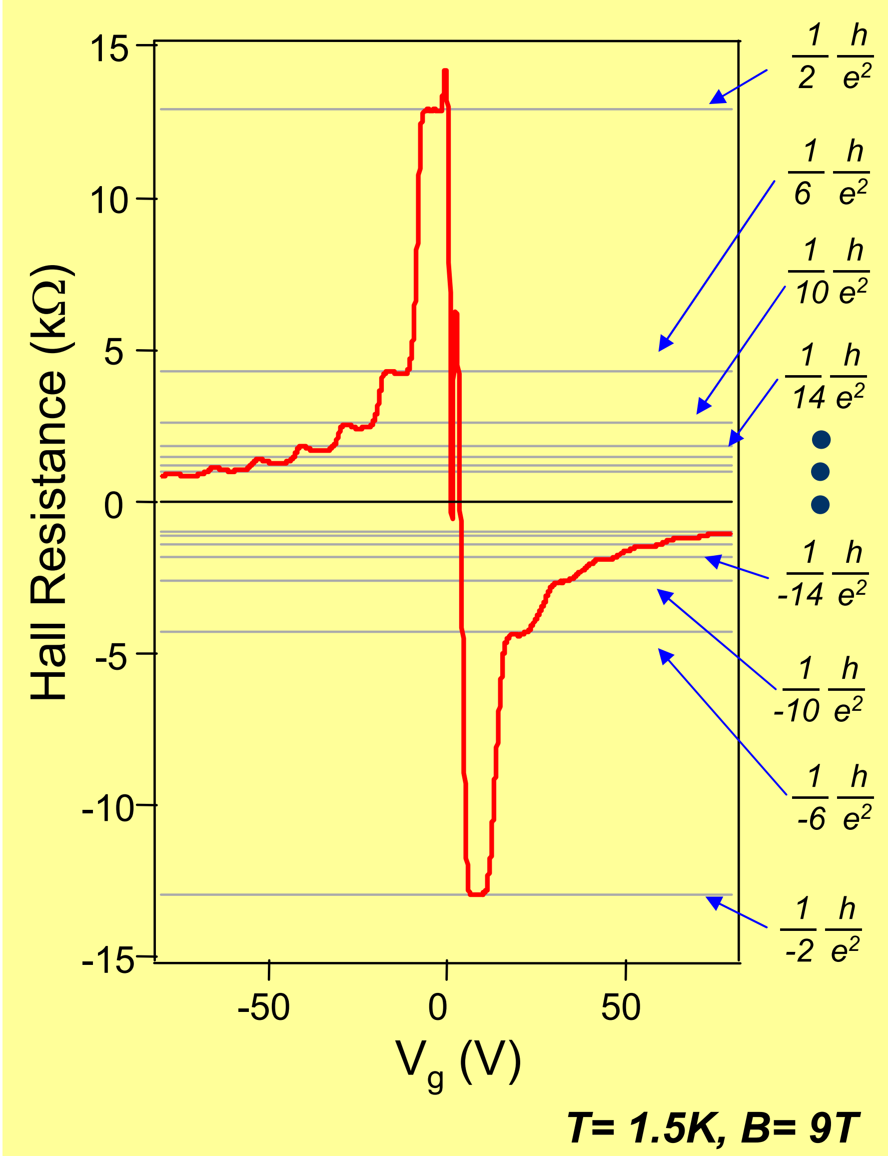
Graphene

- Vanishing carrier mass near Dirac point
- Strict electron hole symmetry
- Electron hole degeneracy

$$\omega_c = \frac{eB}{m^*}$$

Quantum Hall Effect in Graphene





Quantization:

$$R_{xy}^{-1} = 4\left(n + \frac{1}{2}\right)\frac{e^2}{h}$$

Relativistic Landau Level and Half Integer QHE

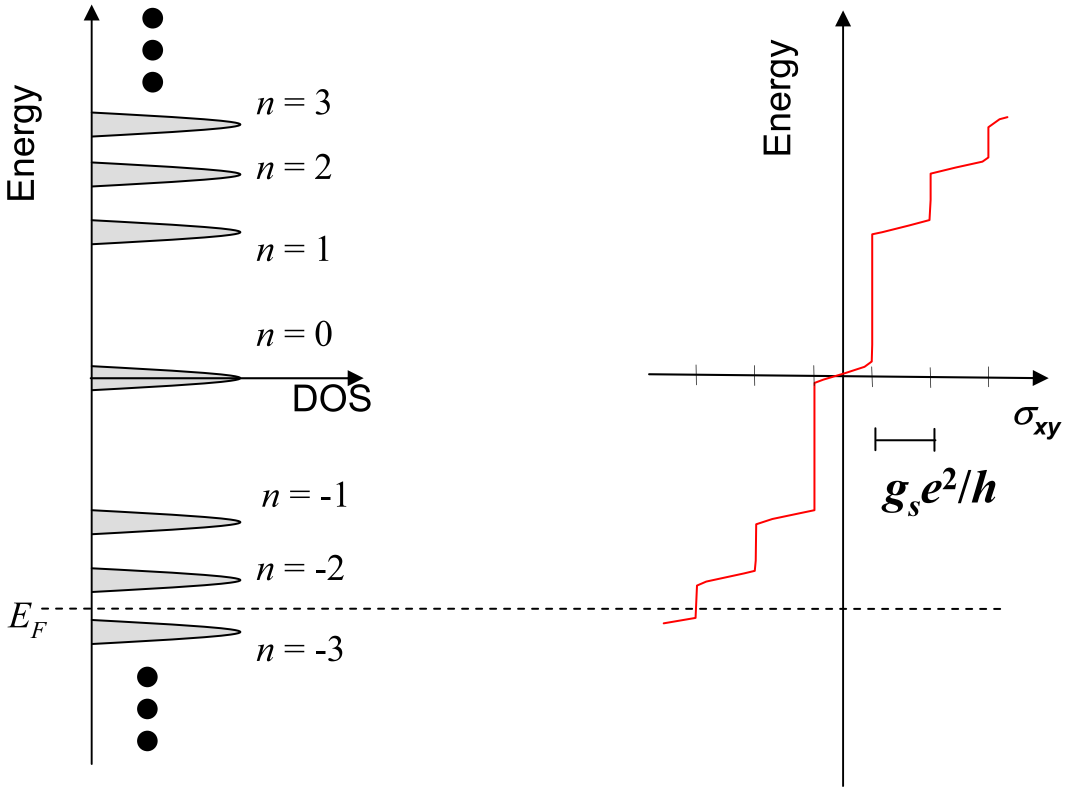
Haldane, PRL (1988)

Landau Level $E_n = \pm\sqrt{2e\hbar v_F^2 |n| B}$

Landau Level Degeneracy

$g_s = 4$

2 for spin and 2 for sublattice



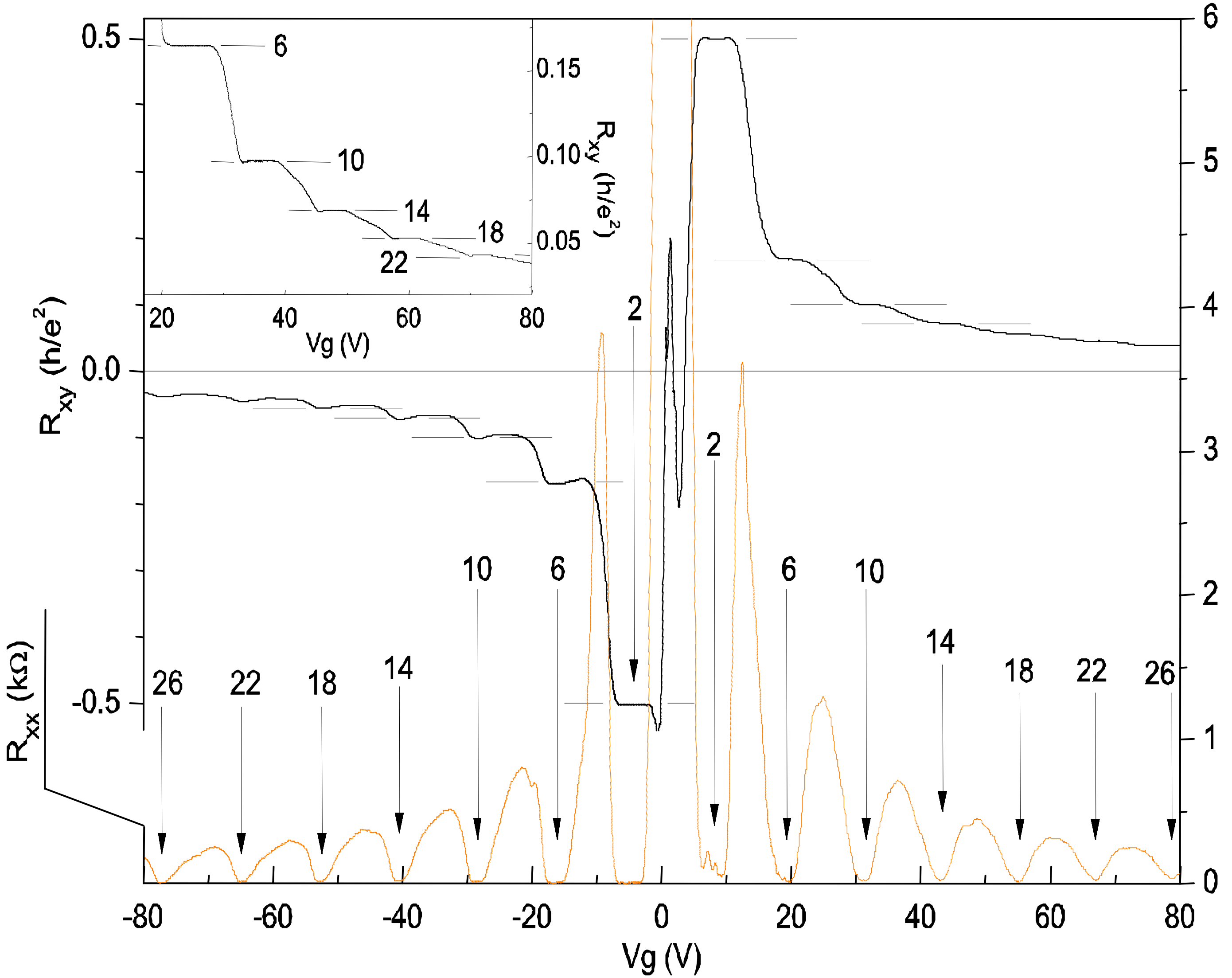
Quantized Condition

$$R_{xy}^{-1} = \pm g_s (n + \frac{1}{2}) \frac{e^2}{h}$$

$$\nu = \pm g_s (n + 1/2)$$

T. Ando et al (2002)

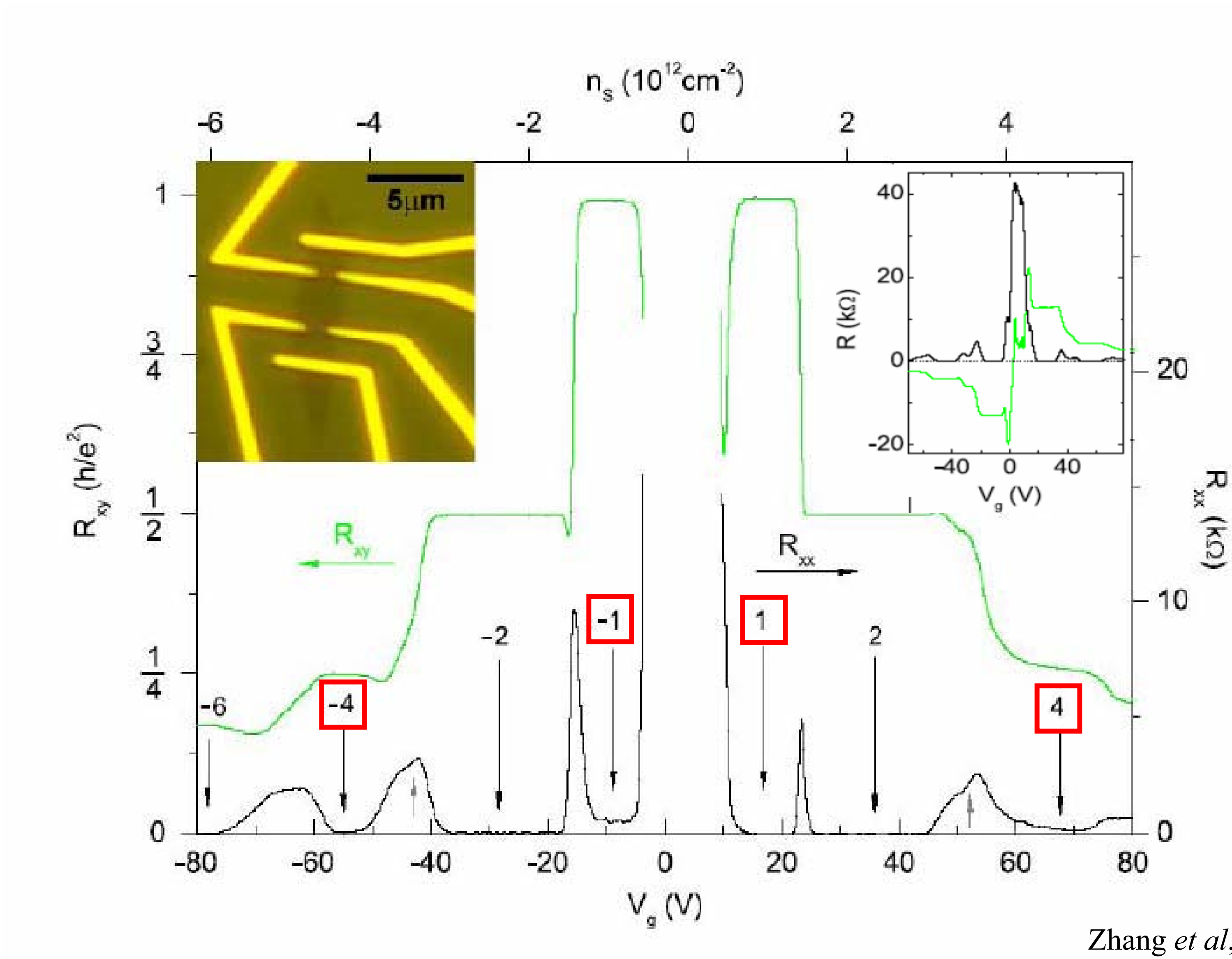
Quantum Hall Effect in Graphene



Mobility
~ 60,000 cm^2/V s

T = 1.7 K
B = 9 T

Quantum Hall Effect in Graphene at High Magnetic Field



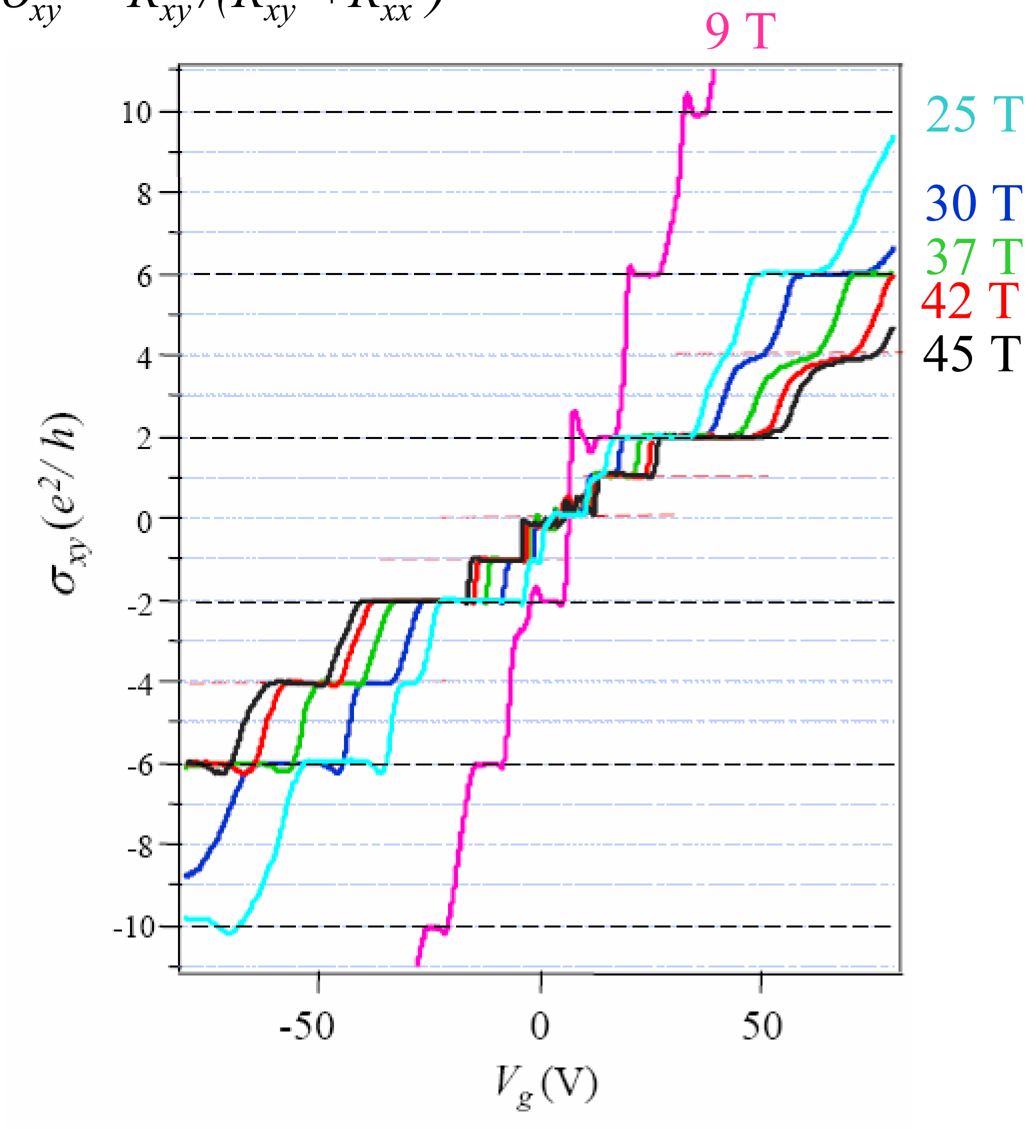
$B = 45$ T

$T = 1.4$ K

Zhang *et al*, Phys. Rev. Lett. (2006)

Splitting of Landau Levels in High Magnetic Fields

$\sigma_{xy} = -R_{xy}/(R_{xy}^2+R_{xx}^2)$



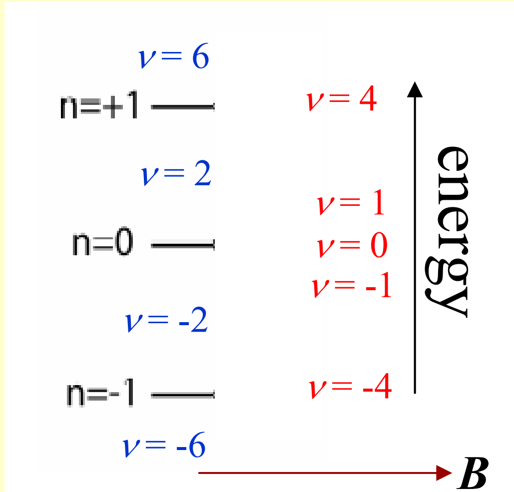
Low fields (B < 10 T)

$\nu = \pm 2,\ \pm 6,\ \pm 10, \ldots$

High fields (B > 20 T)

$\nu = 0,\ \pm 1,\ \pm 2,\ \pm 4,\ \pm 6, \ldots$

Landau Level $E_n = \mathrm{sgn}(n)\sqrt{2e\hbar v_F^2 |n| B}$



Graphene Electronics

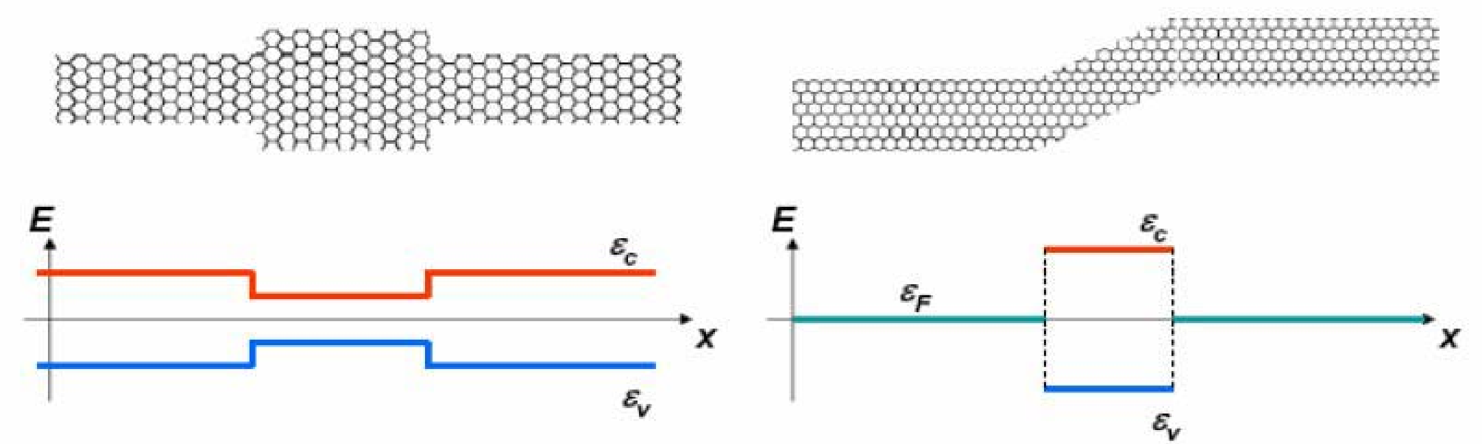
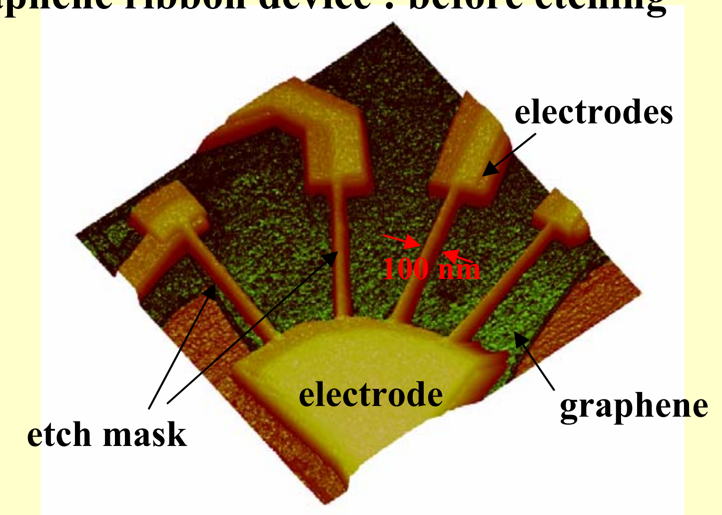
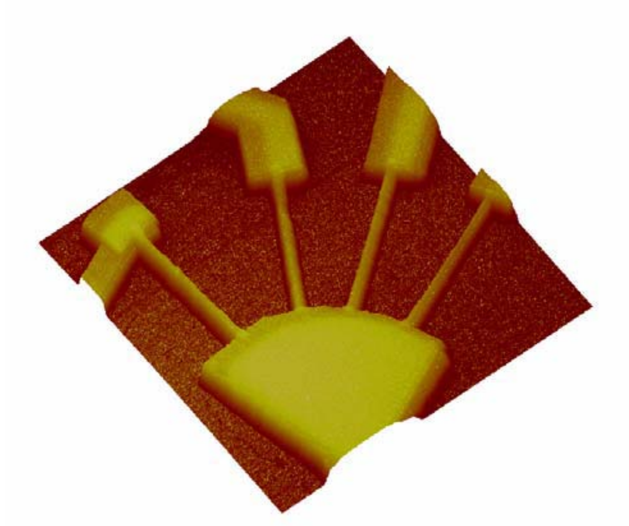


Fig 6. Examples of all graphene device with their band diagram

Graphene ribbon device : before etching

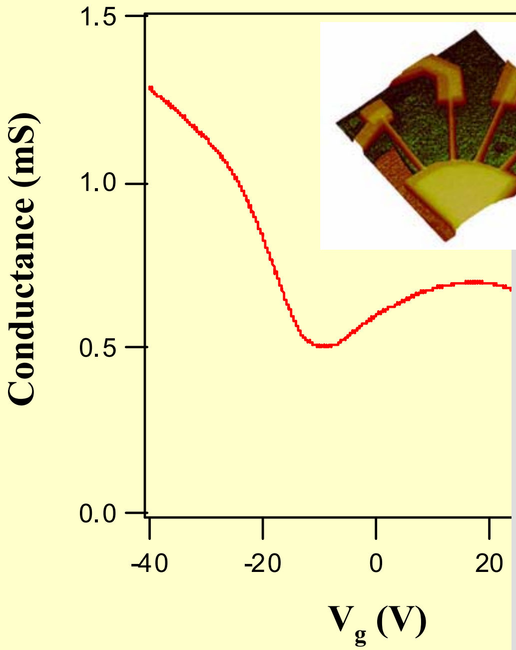


Graphene ribbon device : after etching

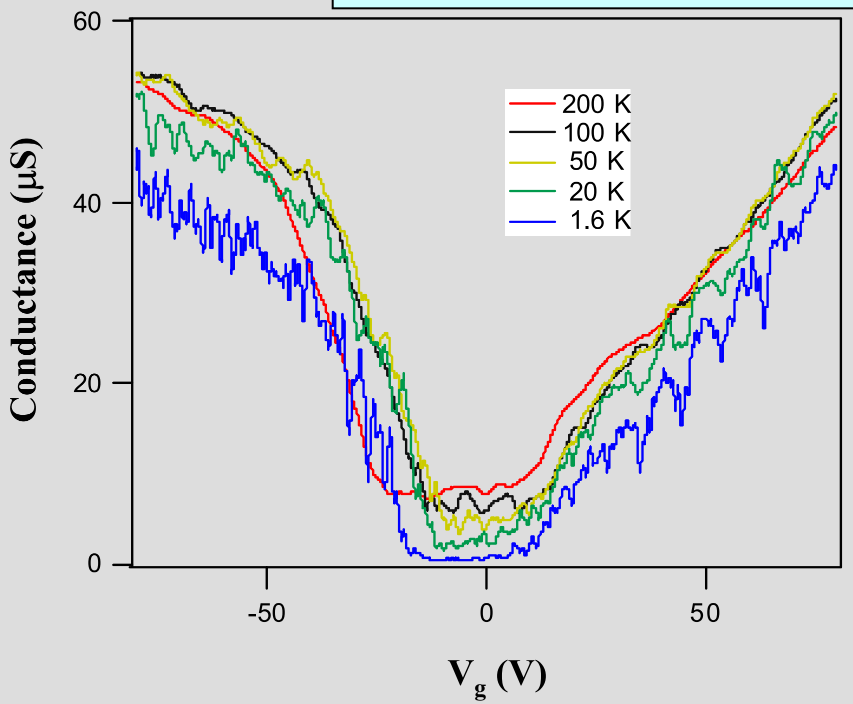


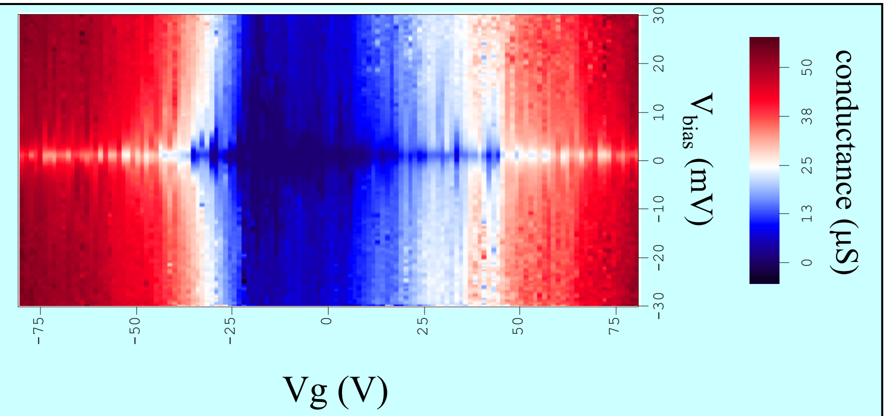
Graphene Ribbon Devices (Preliminary)

Before Etching

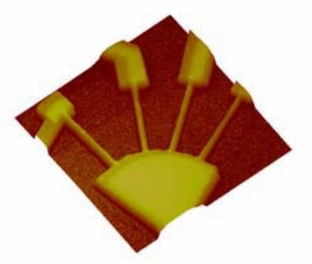


After Etching



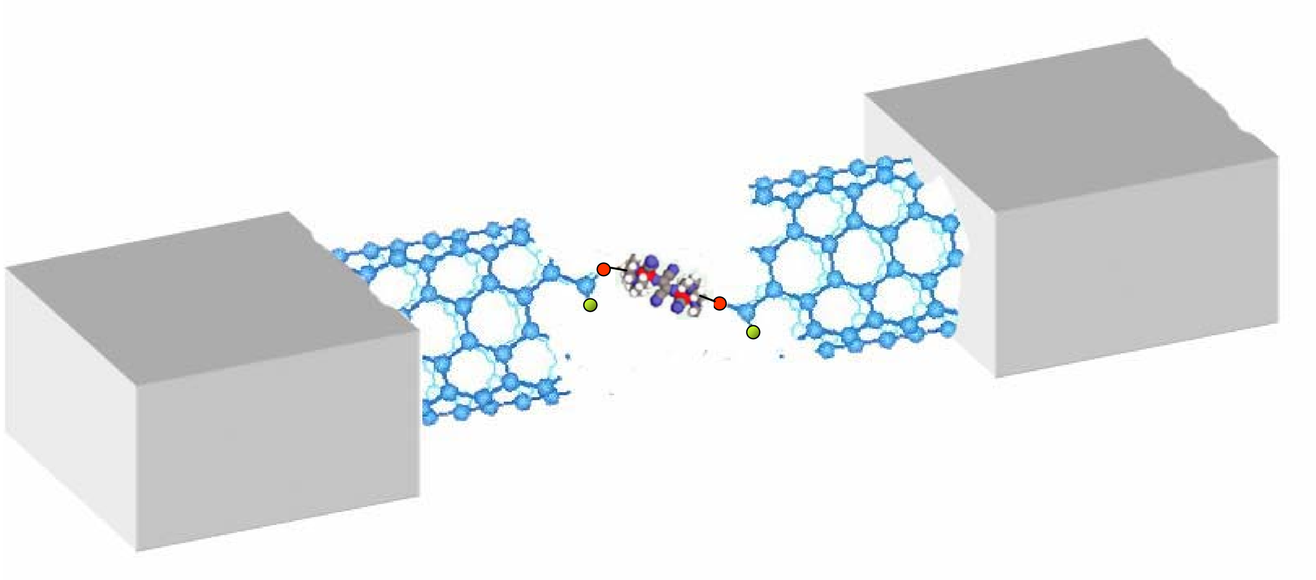


Gap Opening
~ 10 meV
For ~ 80 nm
Graphene ribbon



M. Han, Y. Zhang and P. Kim (2006)

Nanotube Electrodes for Molecular Electronics

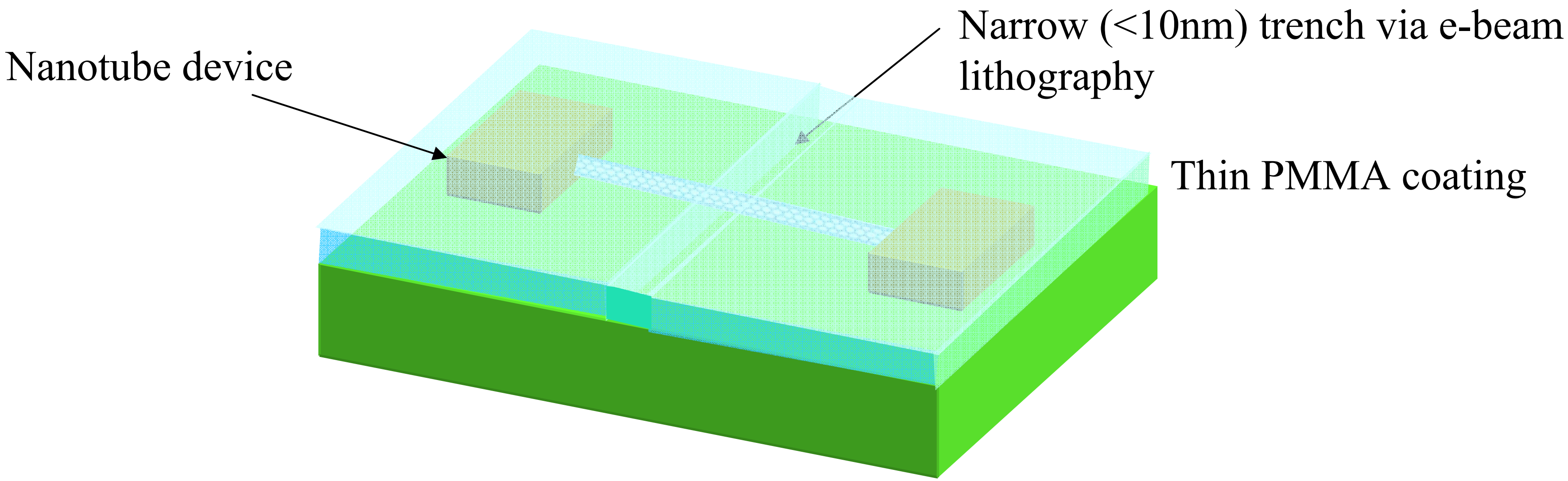


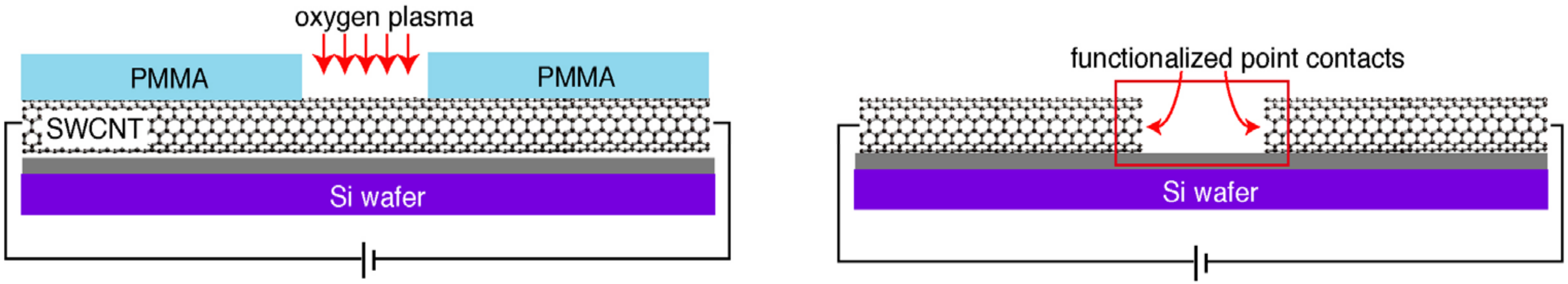
- Nanotubes are inherently small,
  yet compatible to microfabrication processes

- Covalent chemistry between electrode and molecules

- Potentially good conduction via π-bonding network

Nanotube Nanogaps





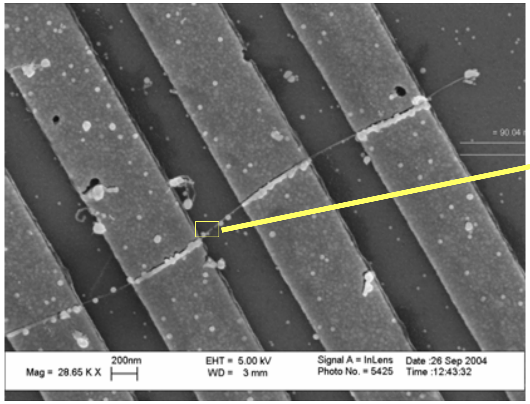
Oxygen Plasma etching creates gaps (0-10 nm) in tubes.

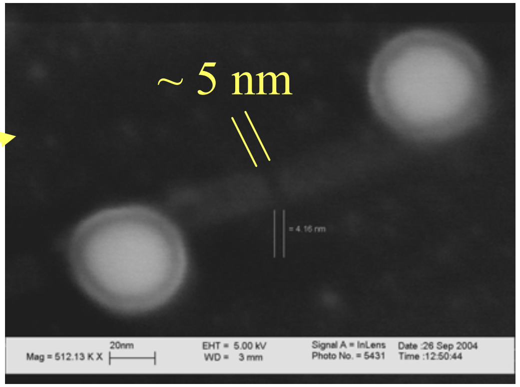
Cut ends likely to be carboxyl-terminated

Hone, Wind, Nuckolls, Brewslow and Kim Collaboration

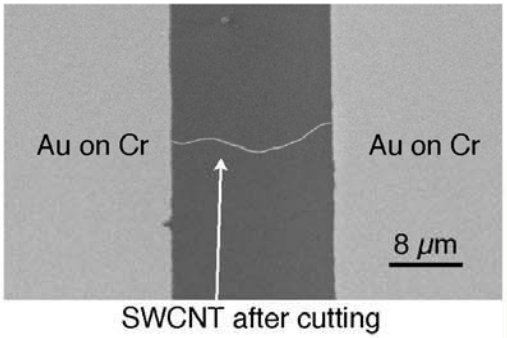
Nanotube Nanogaps

SEM micrograph

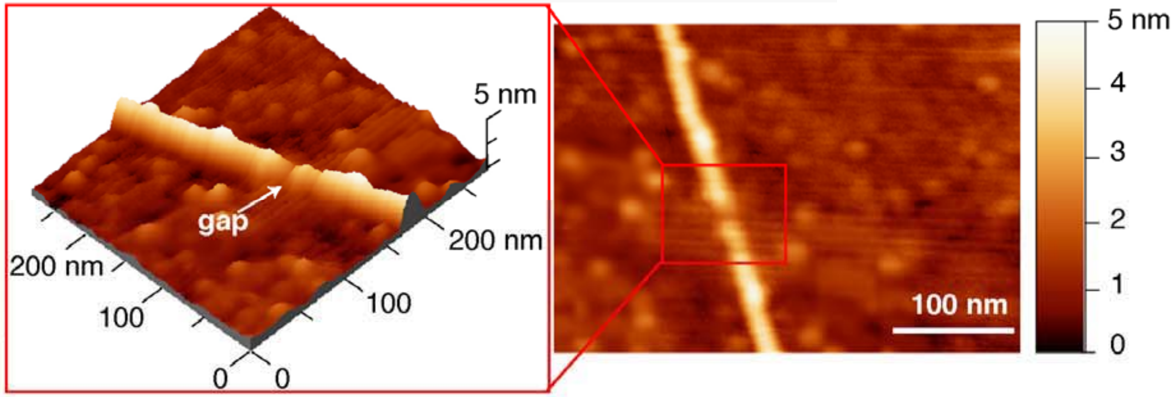




SEM micrograph



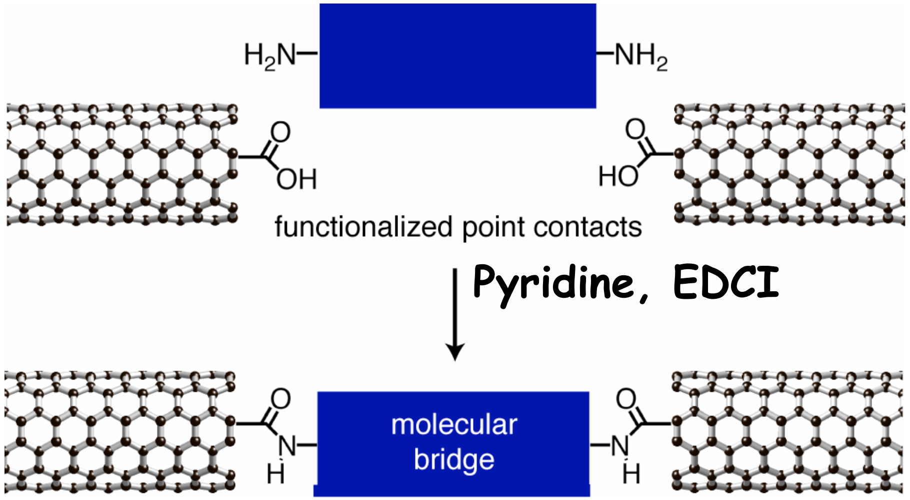
AFM micrograph



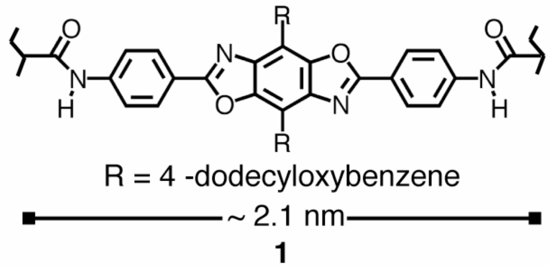
Process are optimized to Yield of cut tubes: 25% of ~2600 devices

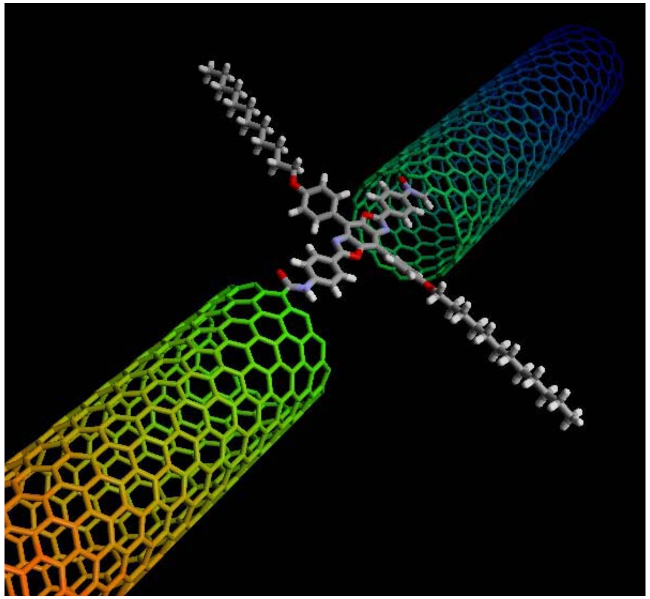
Columbia NSEC (Hone, Wind, Brewslow, Nuckolls, and Kim) Collaboration

Molecular Bridges



Bis-oxazole

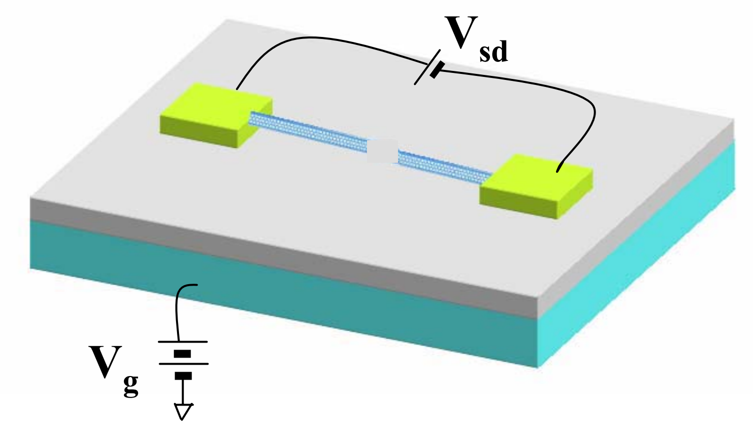




- •Self-assembled
- •Covalently bonded
- •Conduction through π-back bone

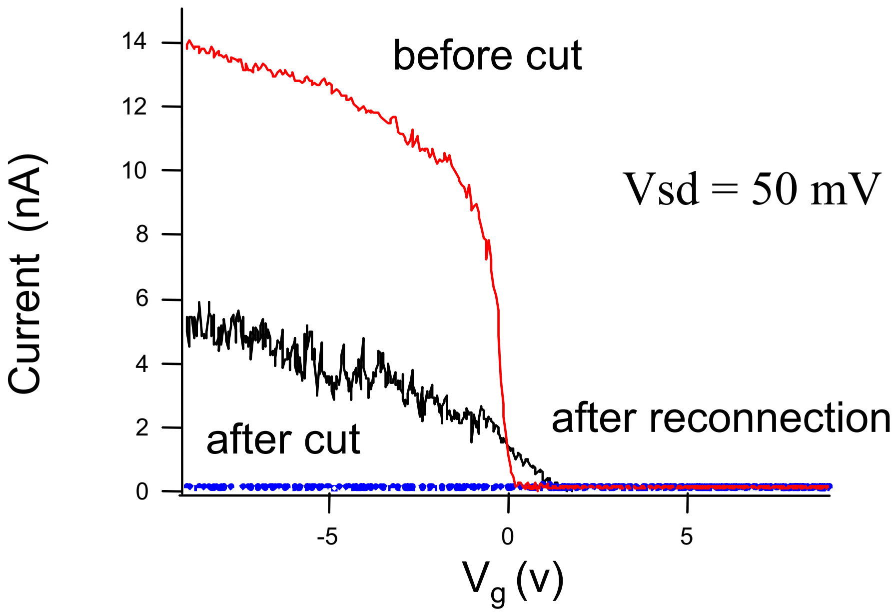
Guo et al., Science (2006)

Does It Work?

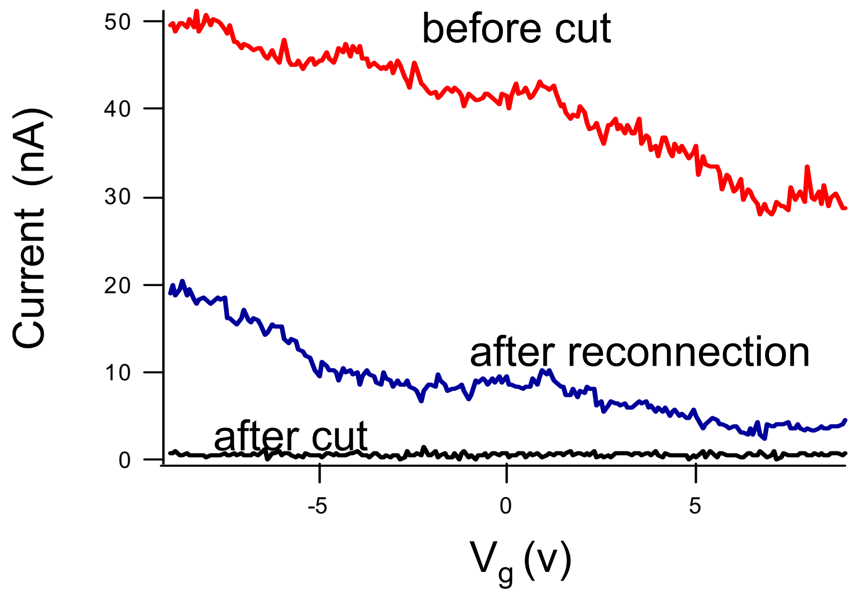


~ 10-15% of reconnection
out of ~ 100 fully cut tubes

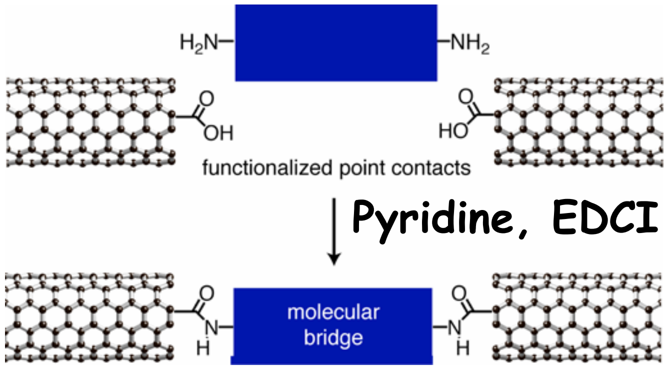
Semiconducting Nanotube + Molecular Bridge



Metallic Nanotube + Molecular Bridge



Control Experiments



Connection
with diamine bisoxazole

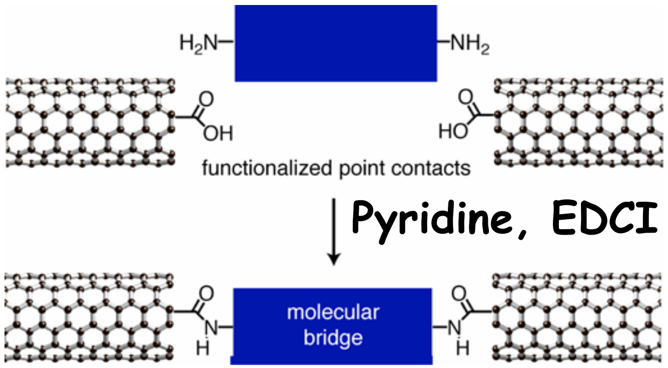
* Pyridine +EDCI without molecules — No connection

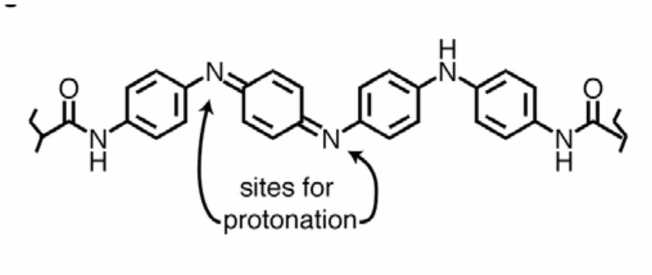
* Bis-oxazole without amines — No connection

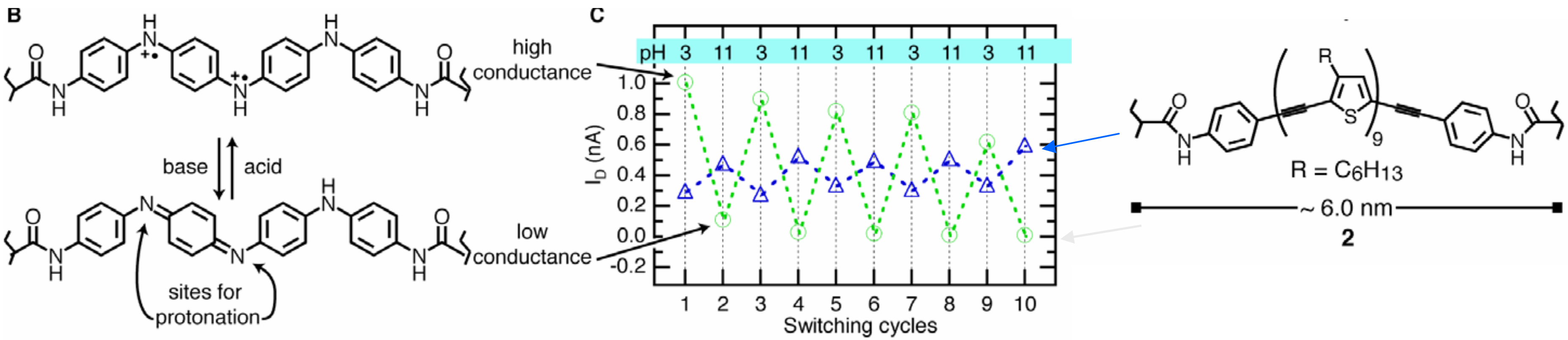
* Bis-oxazole with Monoamine — No connection

* 1,12 dodecane diamine (insulator) — No connection

Oligoaniline: PH sensing

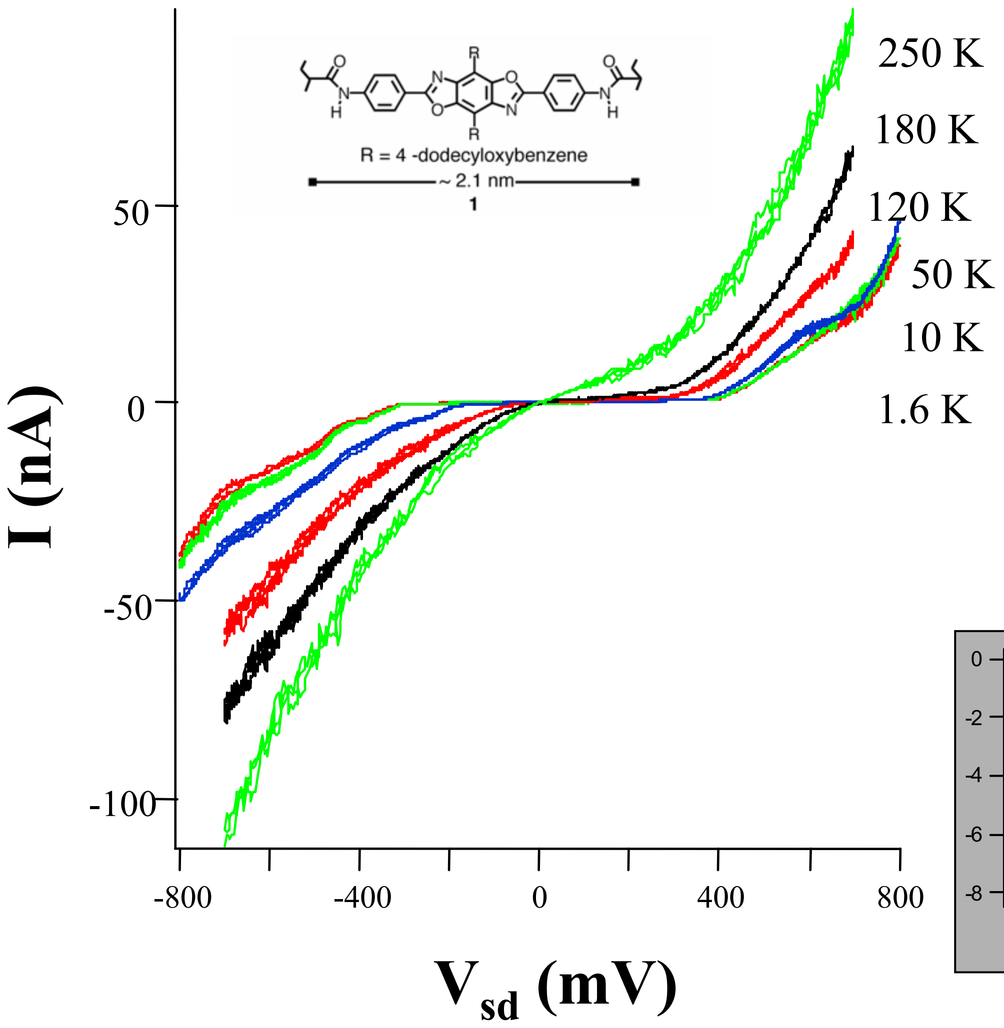


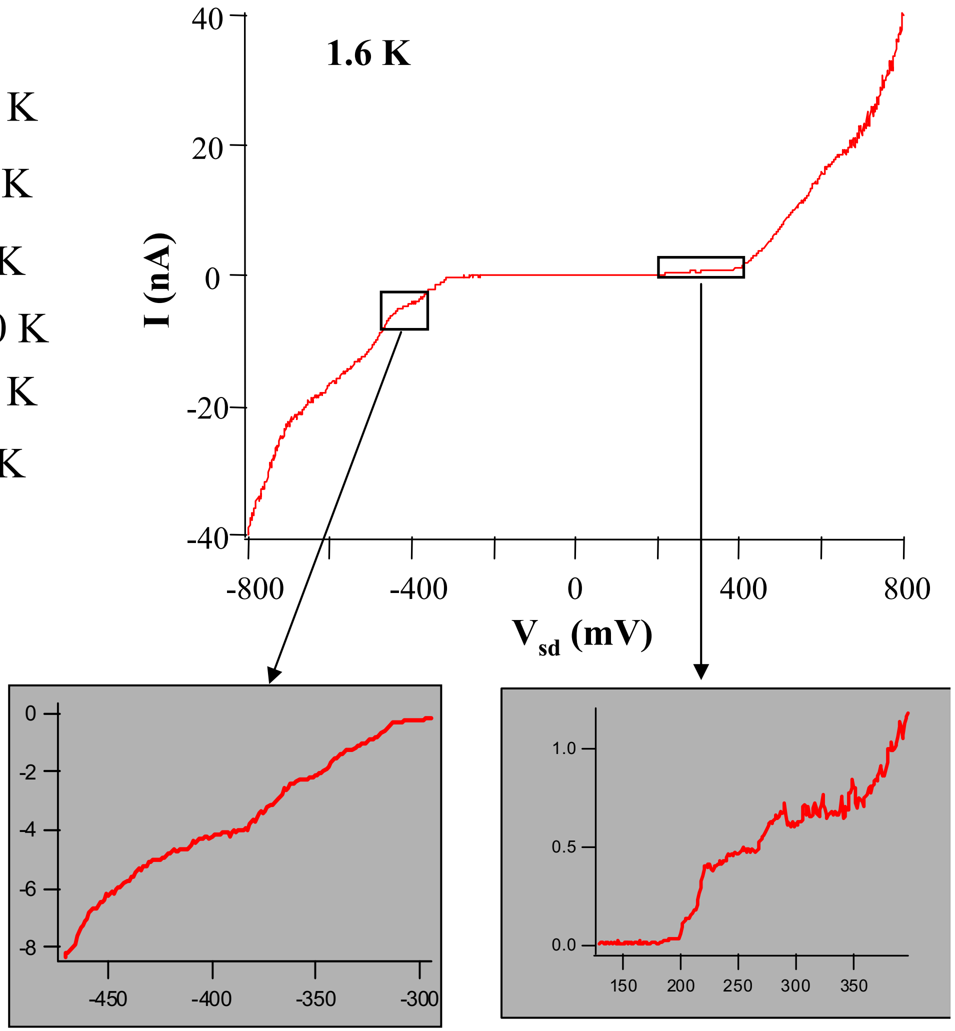




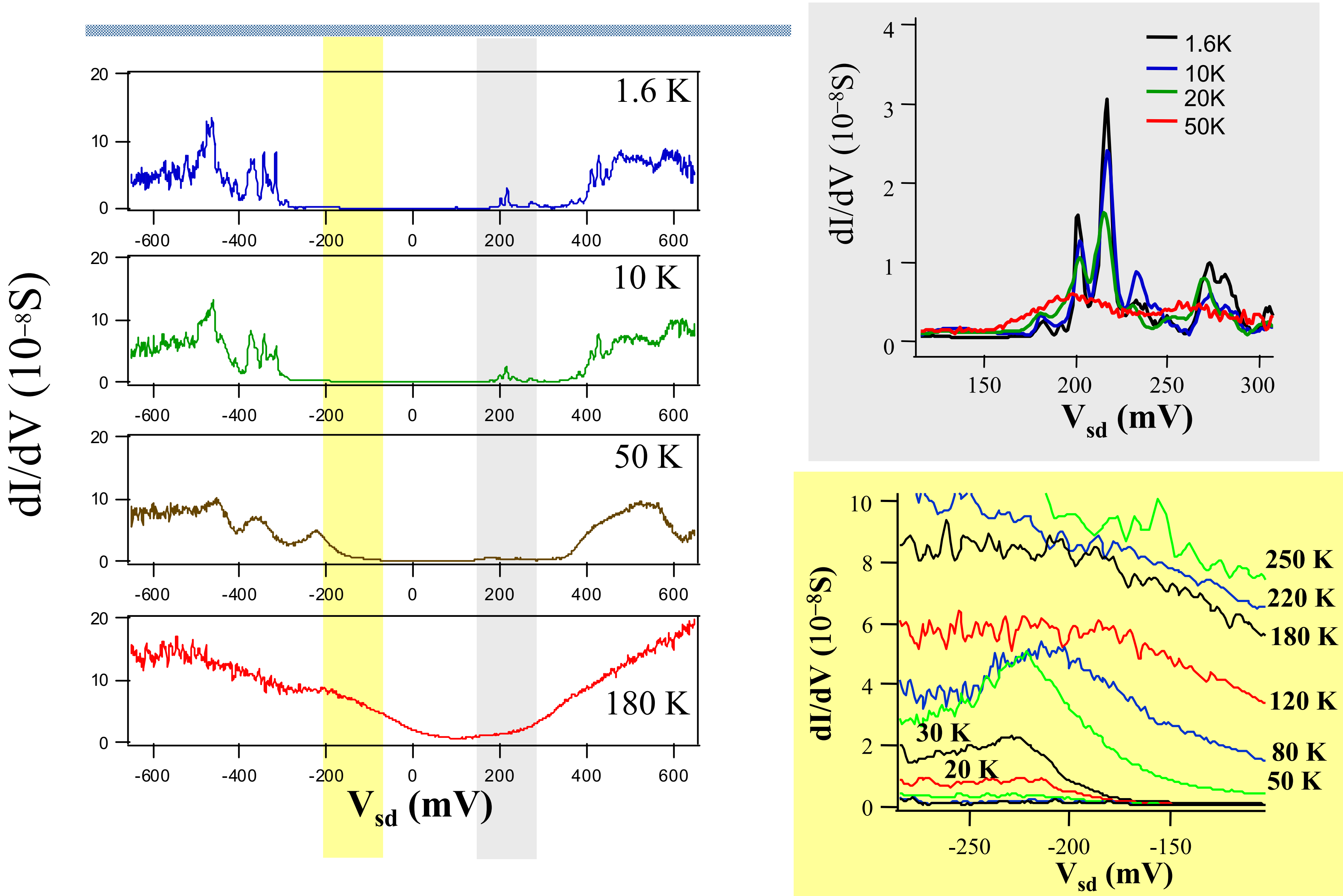
Transport Measurement

Bis-oxazole + metallic SWNT

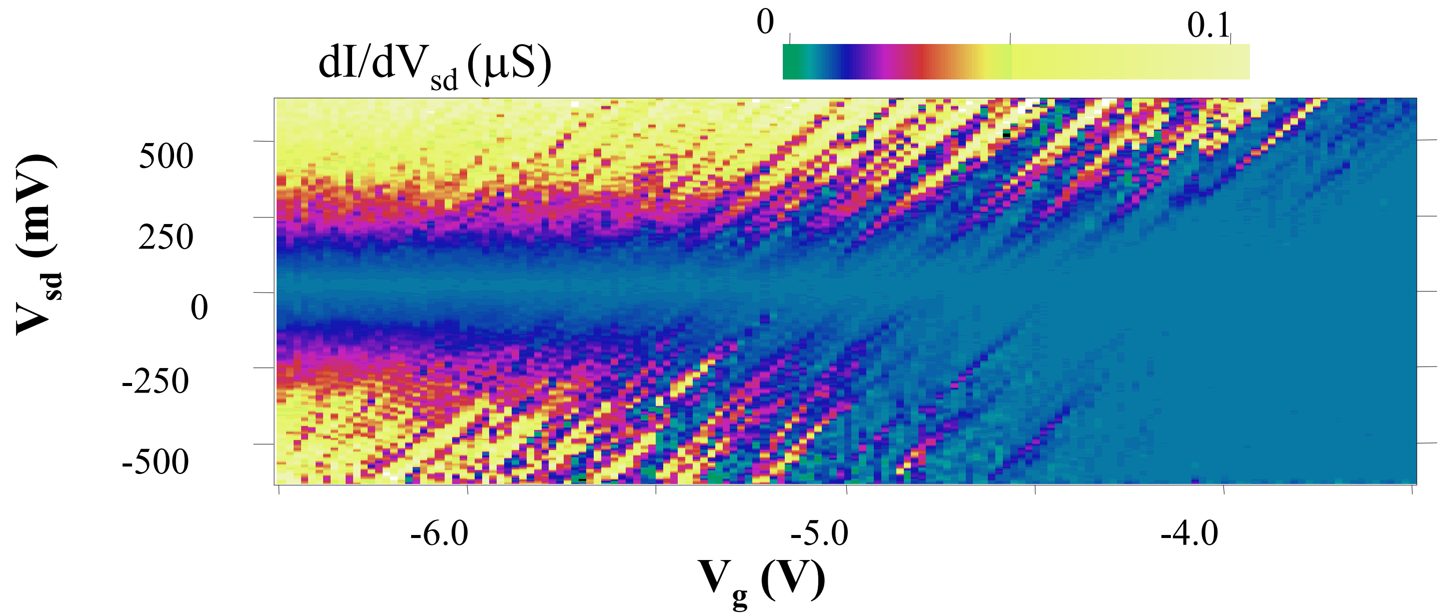


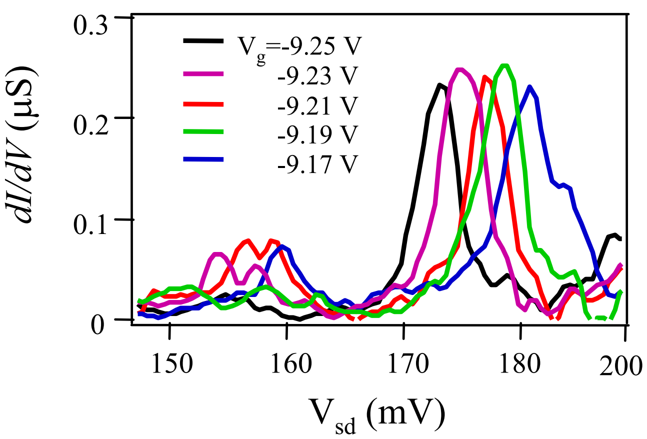


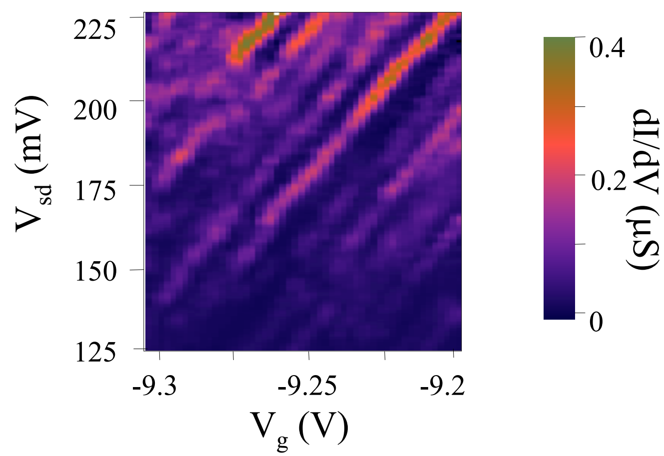
Temperature Dependence Transport Spectroscopy



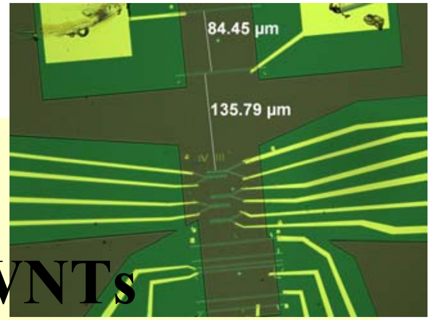
Gate Voltage Dependence





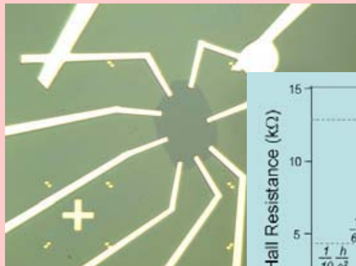


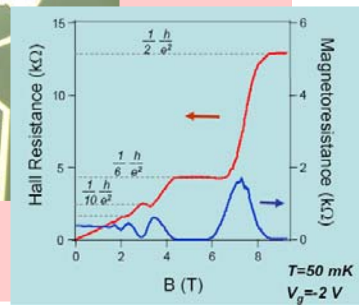
Summary



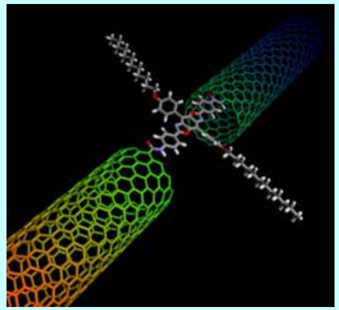
•**Transport in long nanotubes:**
Extremely long mean-free path in SWNTs

•**Transport in graphene:**
Unusual quantum Hall effect
Graphene nano ribbon devices





•**Nanotube electrode for**
single molecular electronics



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